



N A M E

GDR NanoMaterials for Energy applications

E L A B O R A T I O N  
M E S U R E S M E T R O L O G I E  
S I M U L A T I O N S T H E O R I E  
A P P L I C A T I O N S

***GDR NAME***

***Plenary meeting: May 19-21, 2021***

**Workshop 4: Thermal Management**

**May 20<sup>th</sup> 2021**

**Participants:** Younès Ezzahri, Jean-François Robillard, Philippe Ben-Abdallah, Jérémie Drévillon, Nicolas Horny, Karl Joulain, Jérémie Maire, Stéphane Monfray, Elyes Nefzaoui, Stéphane Pailhès and Roberto Simola

**Rencontre plénière du GDR NAME 19-21 mai 2021**



## ● Overview

- Scaling, power, trends, 3D integration, steady-state / transient

## ● Thermal management for Integrated Circuits (IC)

### ● Relevant parameters

- Thermal conductivity
- Thermal interface resistance

### ● Techniques

- Passive: Thermal interface materials

### ● Applications

- Phase Change Materials devices
- Optical components

### ● Challenges and perspectives

## ● Radiative cooling and heating

### ● Principles

### ● Applications

- Daytime radiative cooling
- Nighttime radiative cooling
- Radiative condensers (black silicon)

### ● Challenges and perspectives

## ● Thermotronics

### ● Overview

- Historic breakthroughs in electronics
- A variety of thermal analogues to the electrical components
- Analogies between linear electrical and thermal components

### ● Thermal rectifiers and thermal diodes

### ● Thermal regulators and thermal switches

### ● Thermal transistors

### ● Thermal logical gates and memories

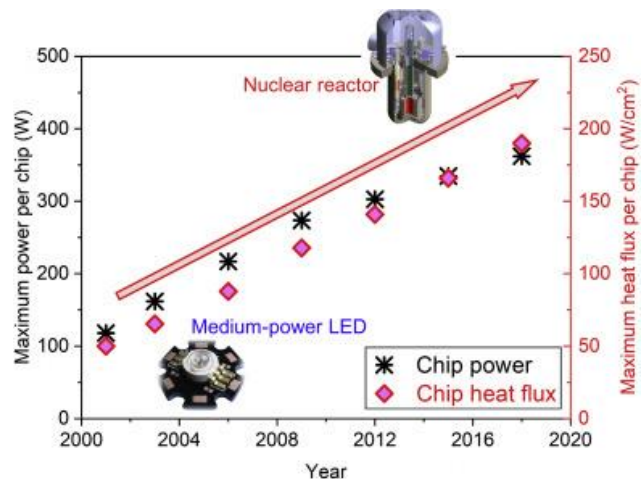
### ● Thermal memristors

### ● Active control of heat flux

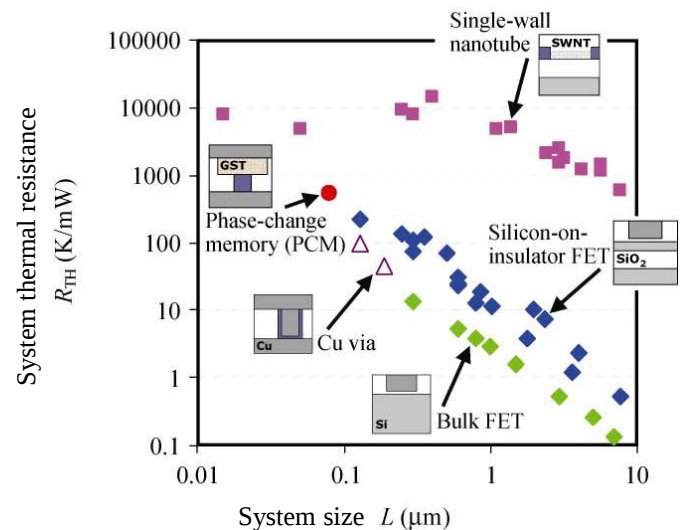
### ● How about the quantum regime?

### ● Challenges and perspectives

## Orders of magnitude



X.-H. Yang and J. Liu, in *Advances in Heat Transfer*,  
50, 187–300 (2018)

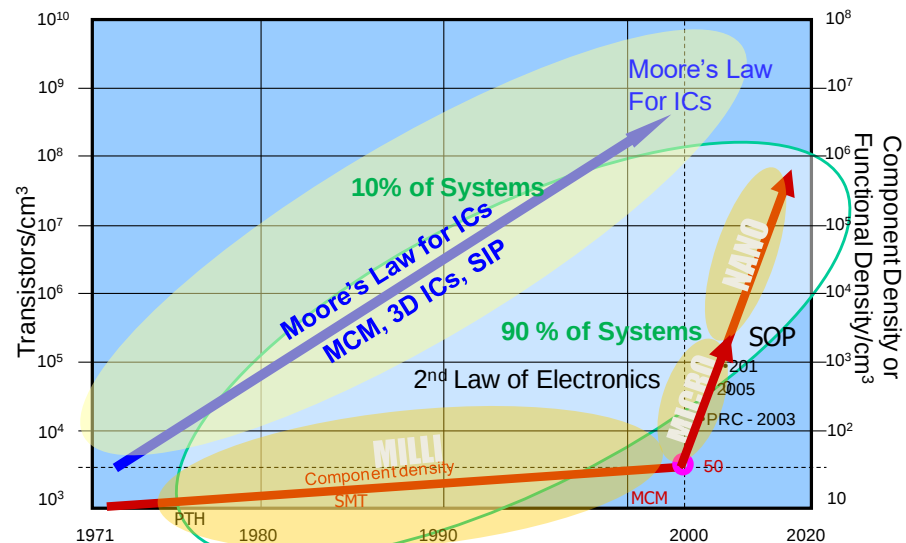


*E. Pop, Nano Res (2010) 3: 147–169*

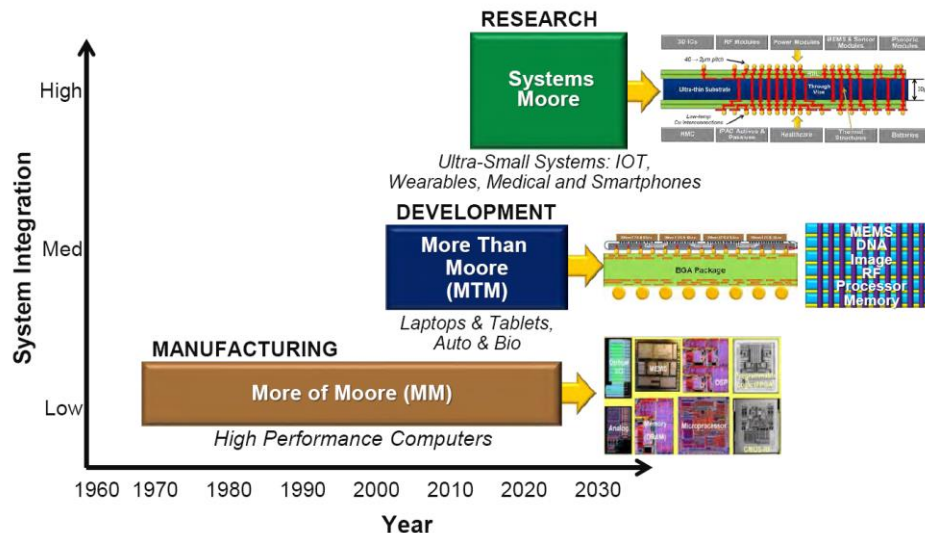
# Overview

## Trends

## From “more Moore” to “system Moore”



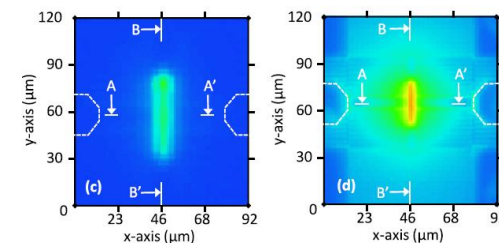
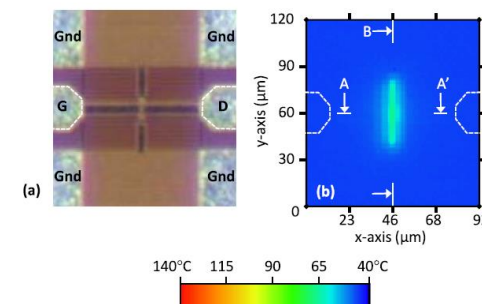
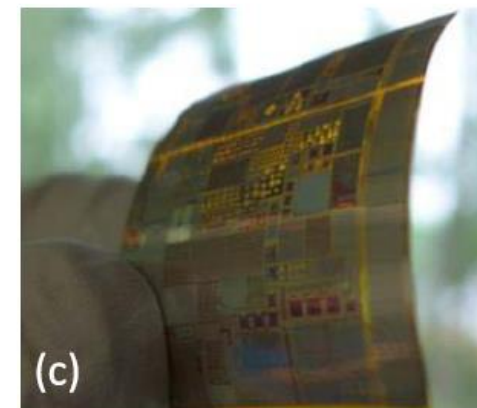
Sources: IBM, Intel



R. Tummala, *System-On-Package (SOP)*, Mc Graw-Hill 2008

## Trends

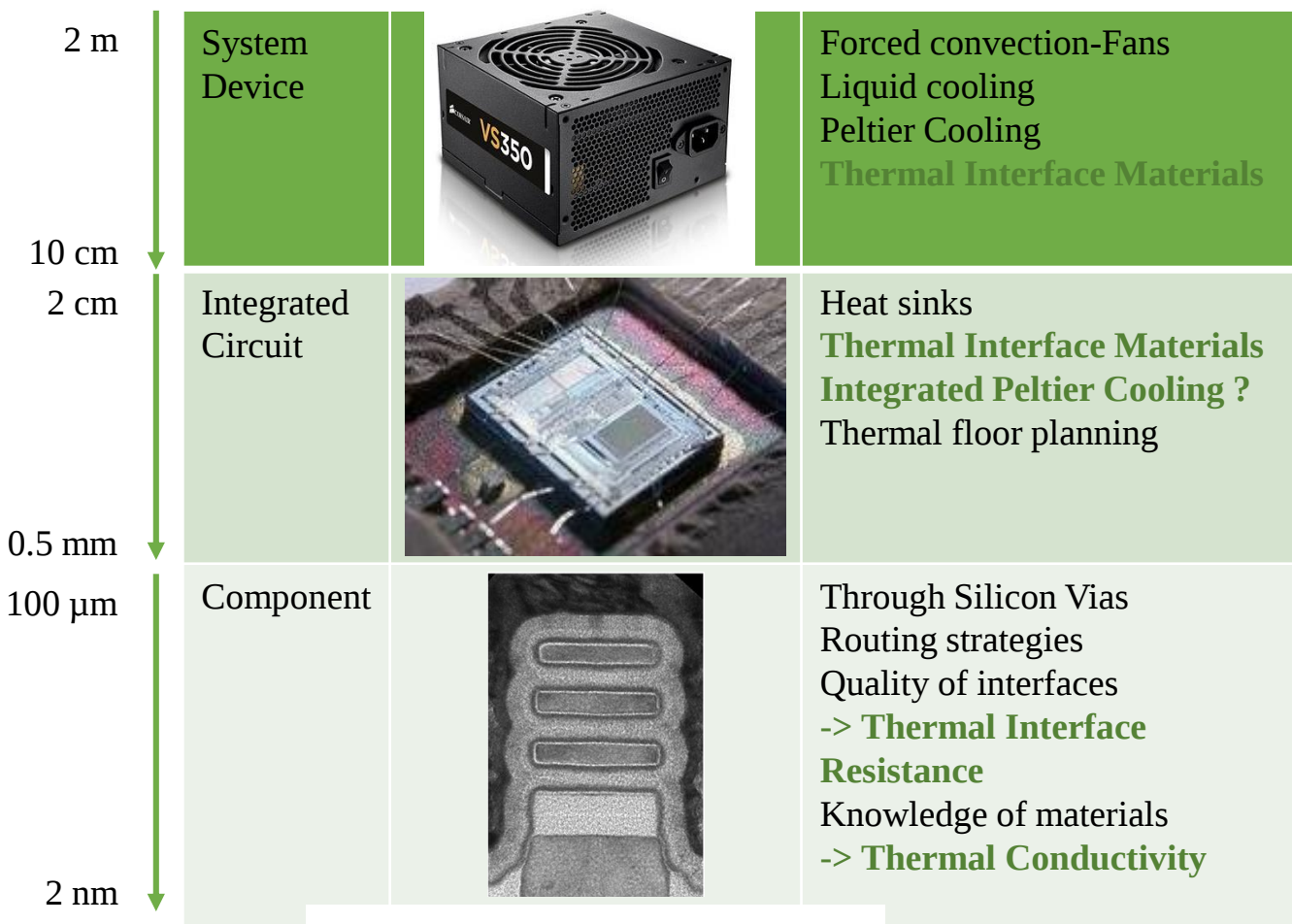
## Flexible electronics



*J. Philippe et al. , Journal of the Electron Devices Society, 7, 973 (2019)*



## Relevant scales



The 2 nm transistor in nanosheet structure.

(Credit: IBM)

(2021)

## Relevant parameters

At component scale, knowledge of

**Thermal conductivity (TC)**

**Thermal boundary resistance (TBR)**

becomes critical for IC design...

## Types of management

### Active

Peltier

Forced convection

### Passive

Heat sinks

Thermal floor planning

Vias-Routing

## Objectives of management

### Component reliability

Heat spreading (data, com, memories...)

### Component performance/efficiency

Noise reduction (imagers, detectors)

### Component operation

« Heat as a resource »

Non-volatile memories (PCM)

Thermo-optical modulation

## ● Thermal interface resistance / conductance

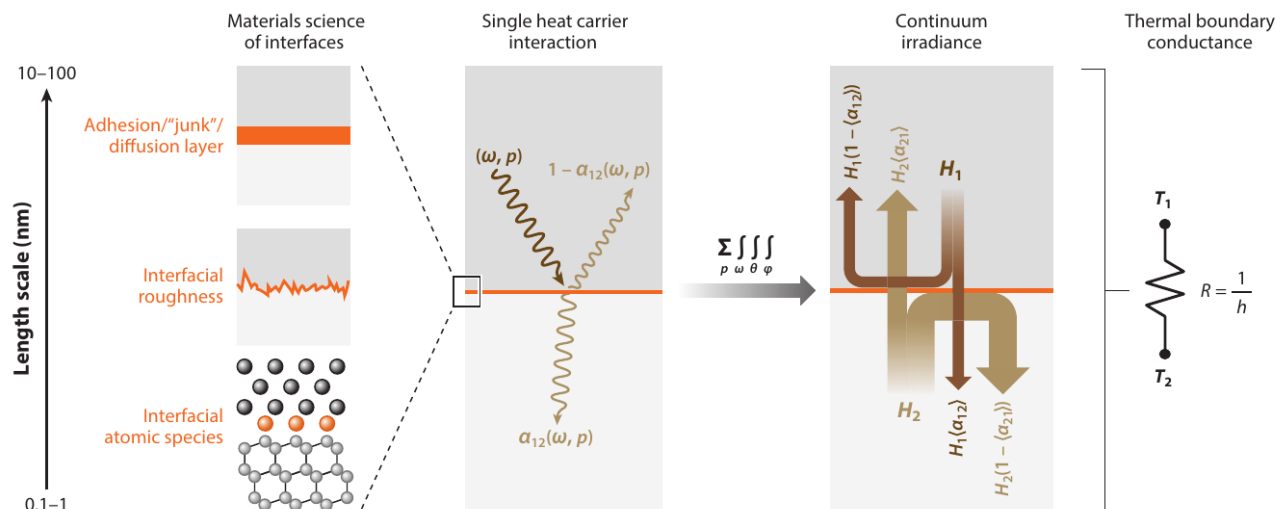
$$h_k = 1/R_k = \frac{\varphi}{\Delta T} [W \cdot m^{-2} \cdot K^{-1}]$$

**Kapitza conductance** technically refers to the conductance across an infinitesimally thin (atomically perfect and abrupt) surface or interface.

However, **Thermal Boundary Conductance** can refer to a more general, spatially broad interfacial region (ex :phonon scattering a few atomic layers away from the actual “interface” can dictate the reported  $h_k$ ).

### Main factors $h_k$ for solid/solid

- Quality of the interface (roughness, oxyde)
- Strength of interatomic interactions at the interface
- Dispersion and density of states (DOS) for energy carriers
- Temperature
- Pressure



- Hopkins, P. E. (2013). “Thermal transport across solid interfaces with nanoscale imperfections: effects of roughness, disorder, dislocations, and bonding on thermal boundary conductance.” *International Scholarly Research Notices*, 2013.
- Monachon, C. et al. , *Annual Review of Materials Research*, **46**, 433-463.
- Maité Blanck et al, *J. Appl. Phys.* **125**, 095302 (2019)
- A. Giri, and P. E. Hopkins, *Advanced Functional Materials*, **30**(8), 1903857 (2020)

## ● Thermal interface resistance / conductance

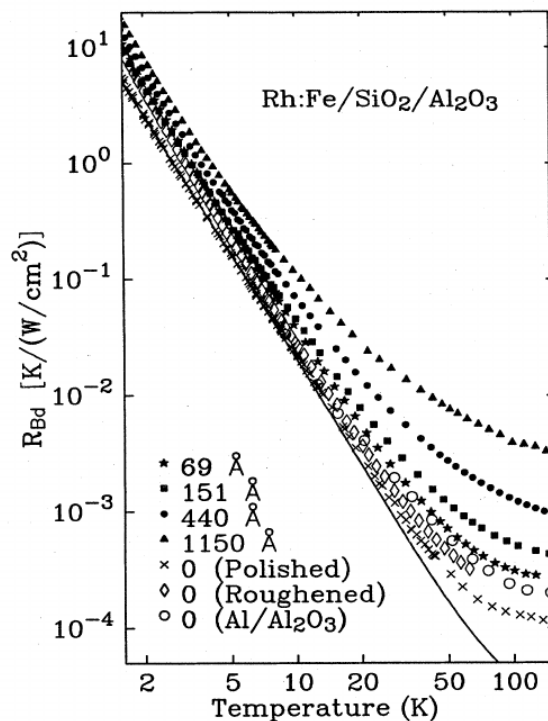
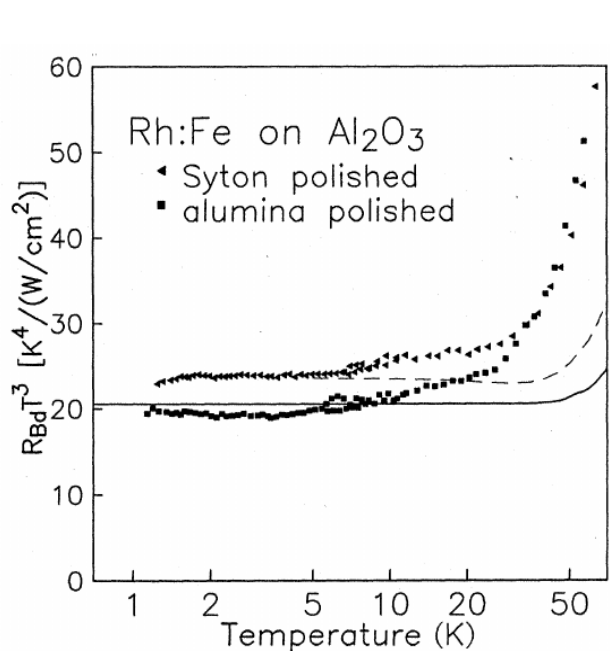
### $T^3$ dependence at low T

« Thermal resistance at interfaces »

E. T. Swartz and R. O. Pohl, *Appl. Phys. Lett.* **51**, 2200 (1987)

« Thermal boundary resistance »

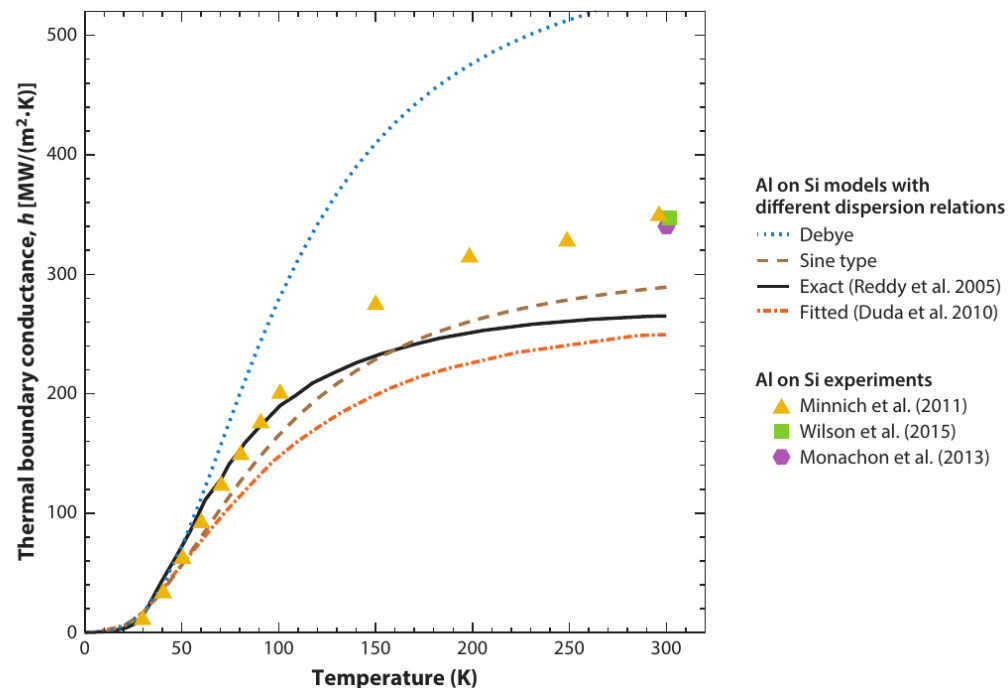
E. T. Swartz and R. O. Pohl, *Rev. Mod. Phys.* **61**, 605 (1989)



### Diffuse Mismatch model

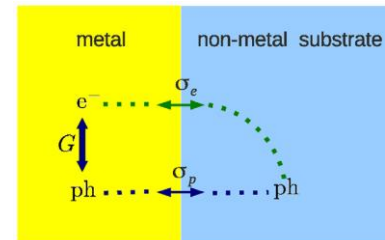
C. Monachon, et al. ,

*Annual Review of Materials Research*, **46**, 433-463.

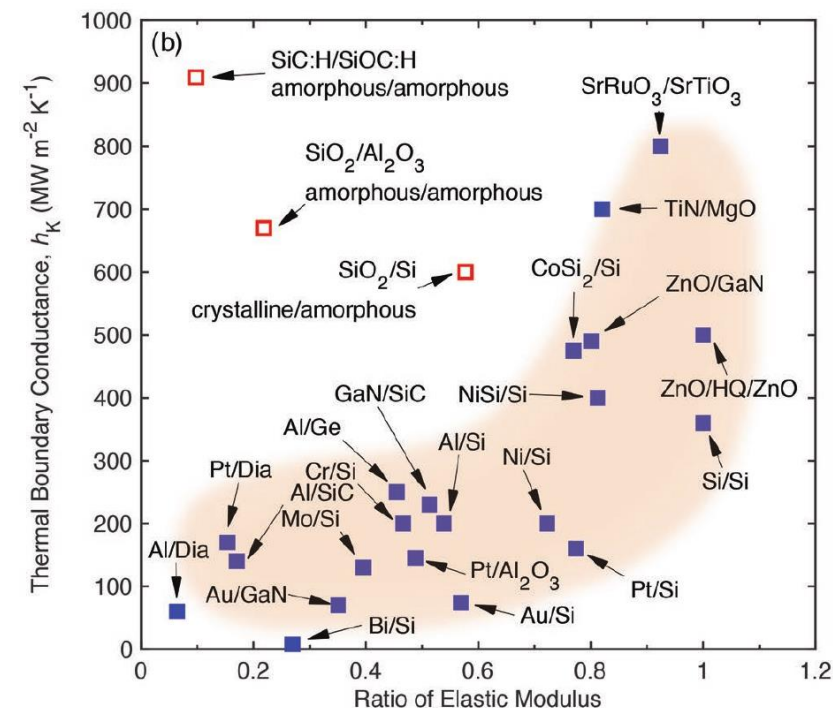
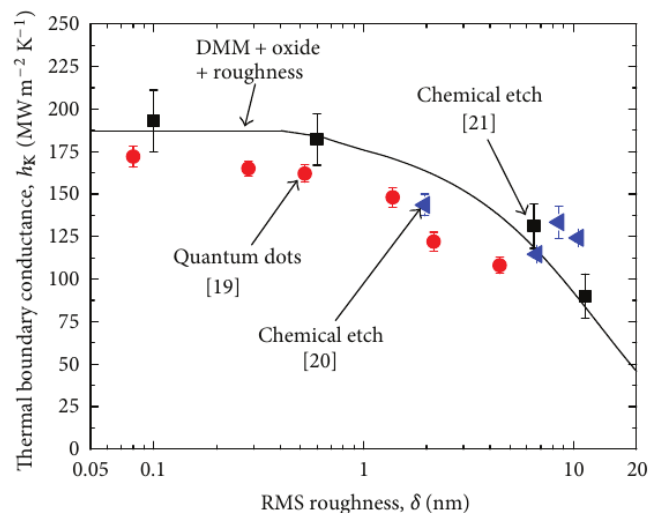
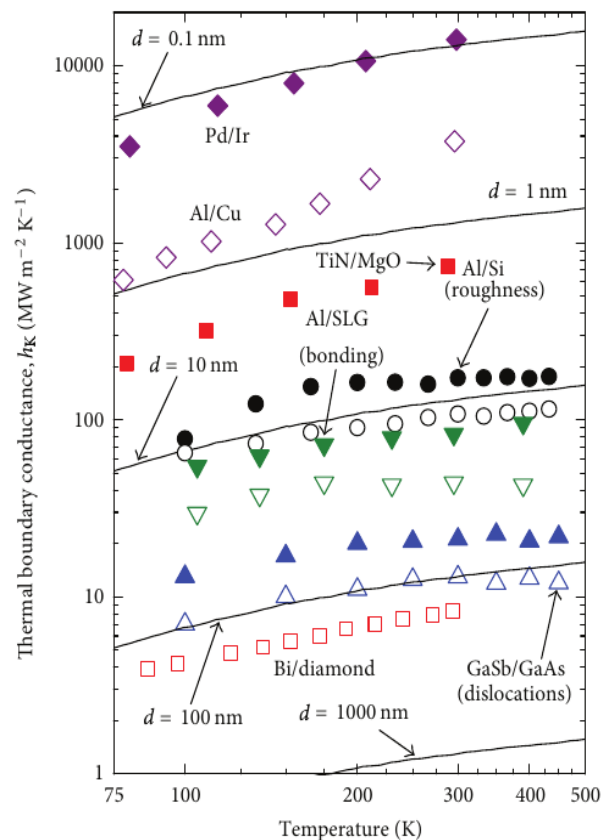


## Thermal interface resistance / conductance

- metal-metal : TBC is dominated by electron transport
- metal-nonmetal : TBC is dominated by phonon transport
- Effect of roughness
- Effects of Lattice Dislocations



J Lombard, F Detcheverry and S Merabia, *J. Phys.: Condens. Matter* 27 (2015).

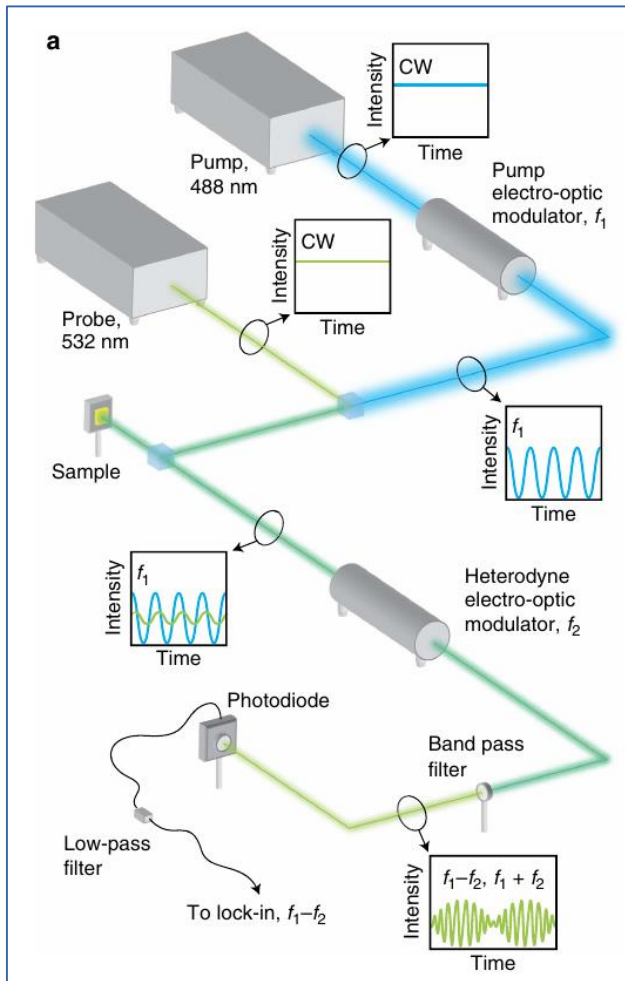


Hopkins, P. E. (2013). "Thermal transport across solid interfaces with nanoscale imperfections: effects of roughness, disorder, dislocations, and bonding on thermal boundary conductance." *International Scholarly Research Notices*, 2013.

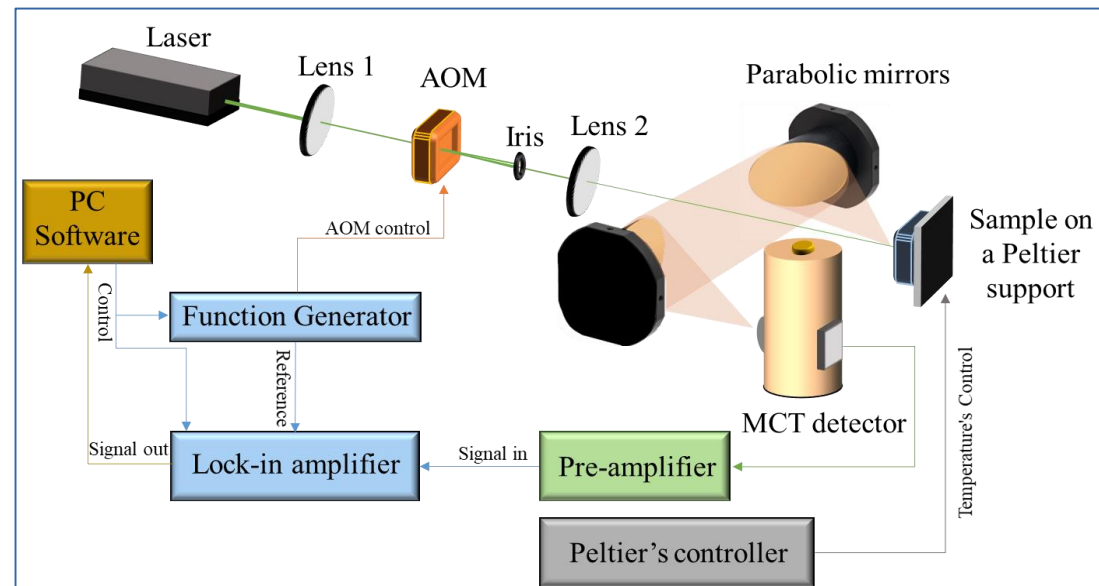
A. Giri, and P. E. Hopkins, *Advanced Functional Materials*, 30(8), 1903857 (2020)

● Thermal interface resistance / conductance    Multiscale thermal characterization techniques

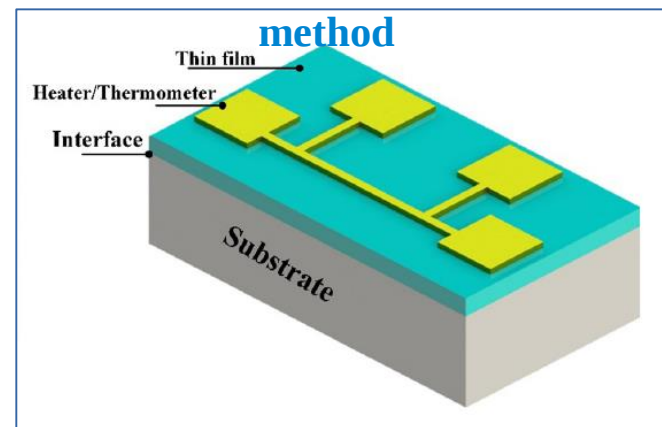
## Time or frequency domain ThermoReflectance



## Time or frequency domain Photothermal Radiometry

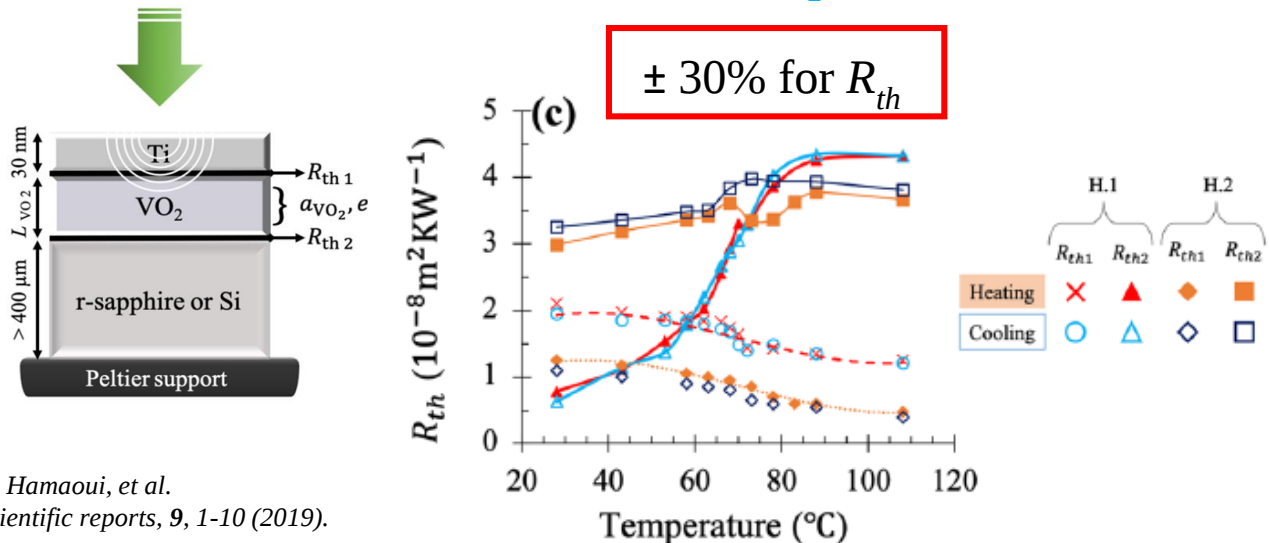


## $3\omega$ method



Applications Phase Change Materials devices

## Thermophysical characterisation of VO<sub>2</sub> thin films hysteresis



G. Hamaoui, et al.  
Scientific reports, 9, 1-10 (2019).

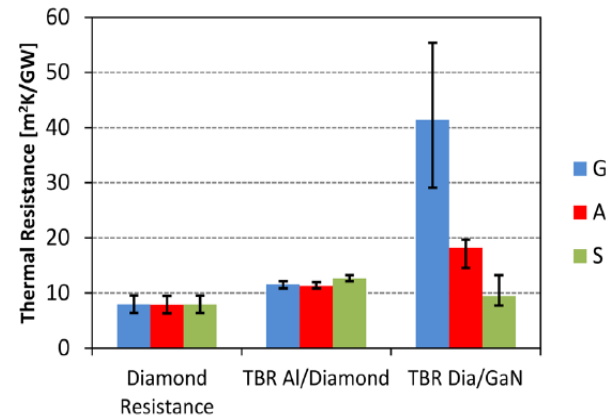
## Low Thermal Boundary Resistance Interfaces for GaN-on-Diamond Devices

| Al:80 nm              | Al:80 nm              | Al:80 nm              |
|-----------------------|-----------------------|-----------------------|
| Diamond:1 μm          | Diamond:1 μm          | Diamond:1 μm          |
| None                  | 5nm AlN               | 5nm SiN               |
| GaN: 500 nm           | GaN: 500 nm           | GaN: 500 nm           |
| AlN Nucleation: 20 nm | AlN Nucleation: 20 nm | AlN Nucleation: 20 nm |
| SiC:500 μm            | SiC:500 μm            | SiC:500 μm            |

None: Sample "G"

AlN: Sample "A"

SiNx: Sample "S"



Yates et al., ACS Appl. Mater. Interfaces 2018, 10, 24302–24309 (2018)

## Electronic contribution in heat transfer at metal-semiconductor and metal silicide-semiconductor interfaces

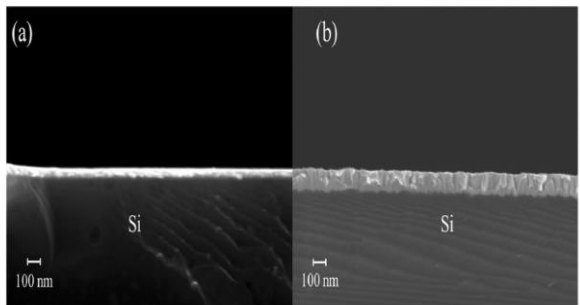
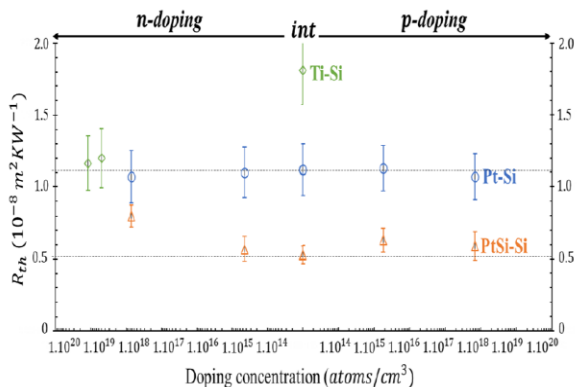


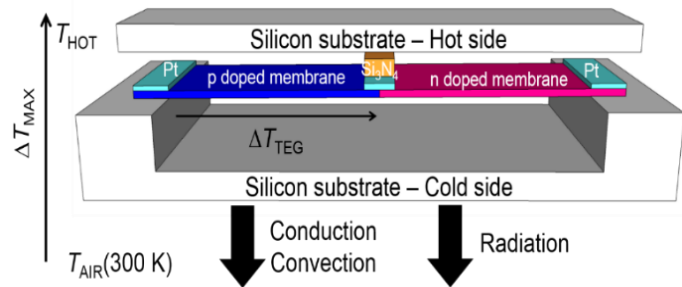
Figure 3. Example of a SEM images for the S3 samples: (a) unannealed Pt-Si and (b) annealed PtSi-Si samples.

G. Hamaoui et al. Scientific reports, 8, 1-9 (2018).

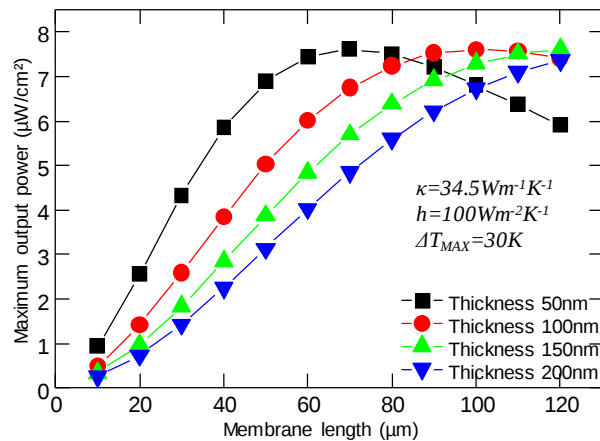


## Applications • Thermoelectric Energy harvesting

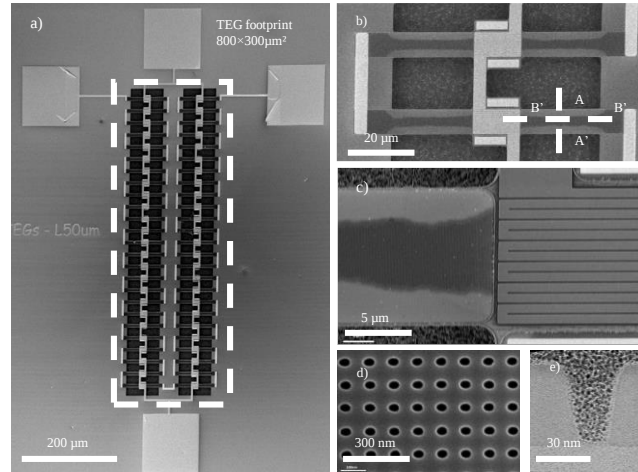
Attempts to integrate membrane-like or NW TE Converters lead to new thermal management issues.  
Mainly related to the vertical to horizontal heat flux redirection  
And air exchange.



Device optimization



### c-Si Membranes



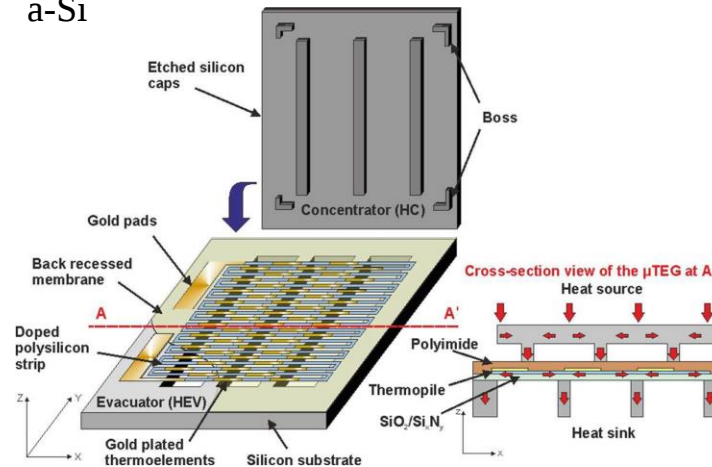
M. Haras et al. *IEEE Electron Device Letters*, 37, 1358 (2016)  
T. M. Bah et al. (in prep.)

### Bi2Te3



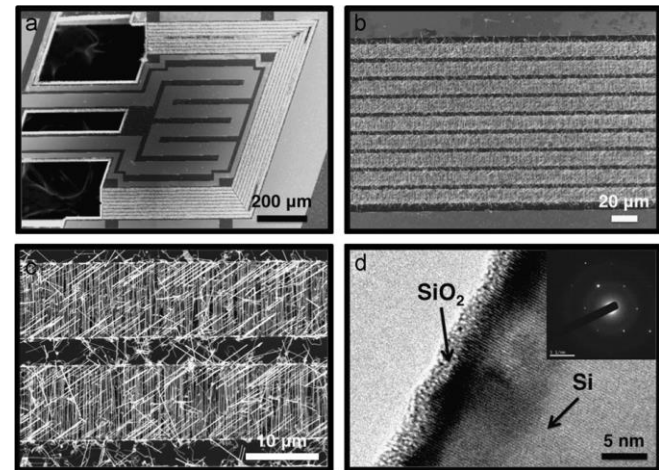
D. Tainoff et al. *Nano Energy* 57 804–810 (2019)

### a-Si



K. Ziouche et al. *Journal Of Microelectromechanical Systems*, 26, 45 (2017)

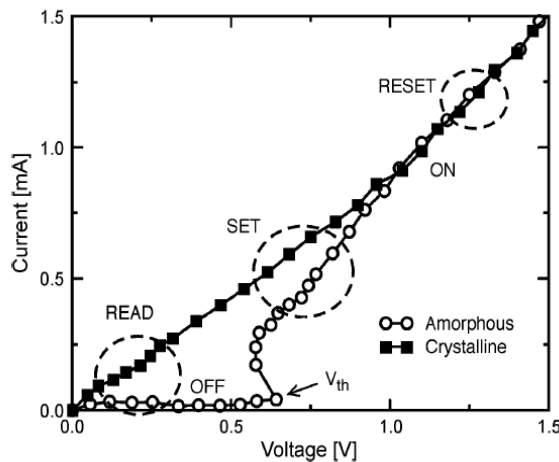
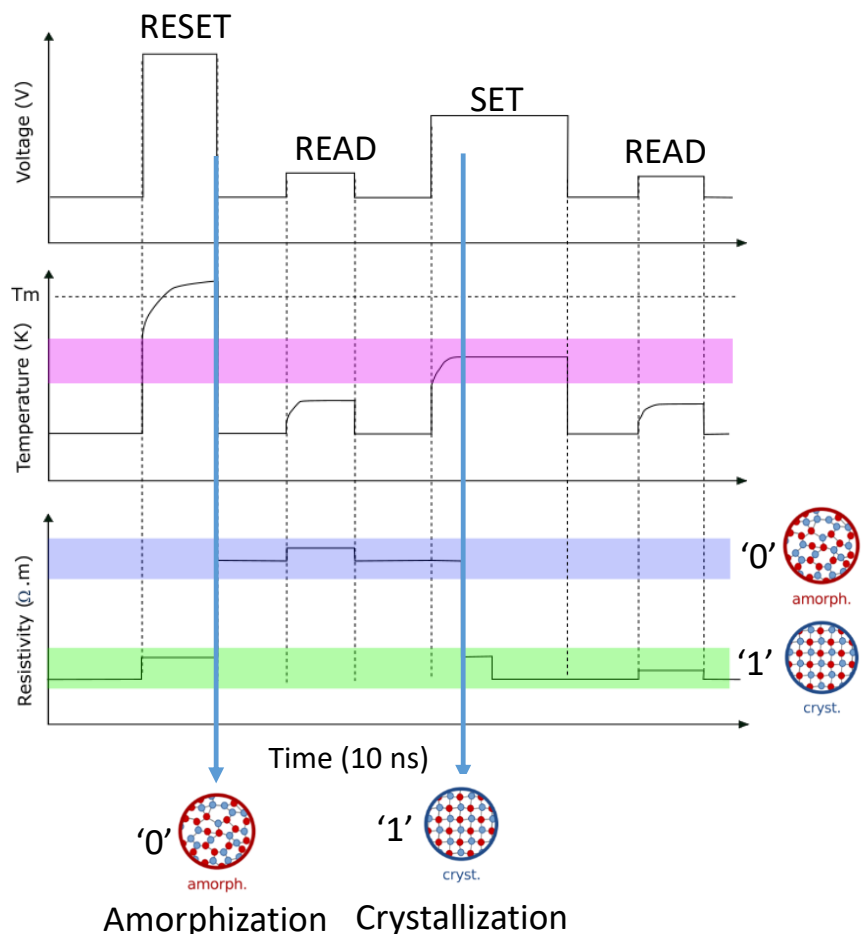
### c-Si NW



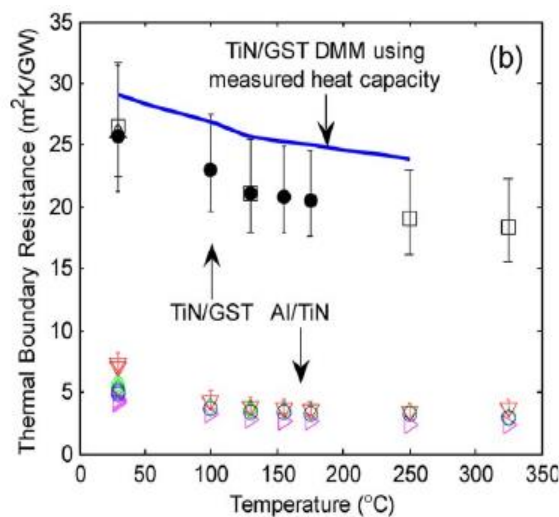
D. Davilà et al. *Nano Energy* 1, 812 (2012)

## Applications • Phase Change Materials devices

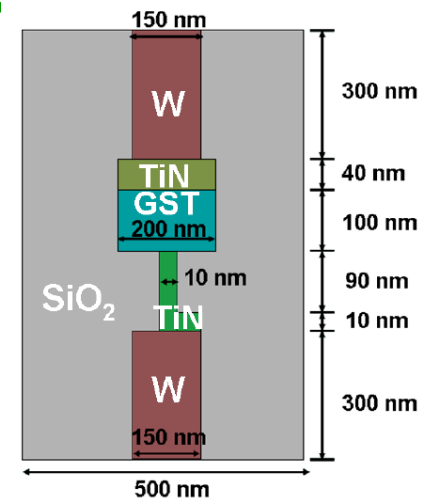
- Transition between amorphous and crystalline phase
- Phase transition – current induced Joule heating
- Information stored in the resistance of the alloy



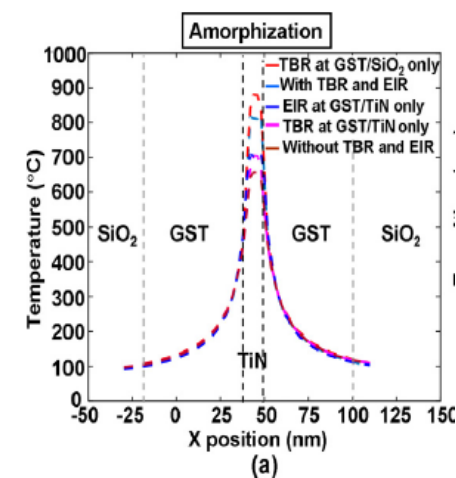
A. Pirovano et al IEEE Trans. Electron Devices, **51**, 452 (2004).



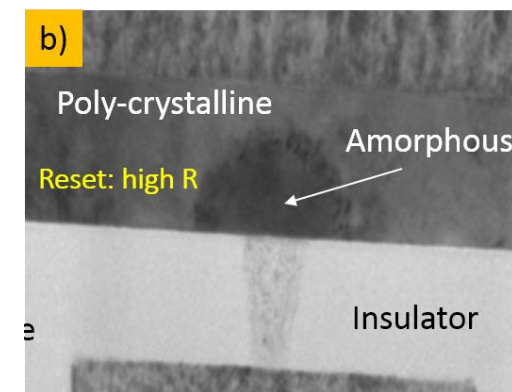
John P. Reifenberg, et al. IEEE Electron Device Letters, **31**, NO. 1, (2010)



J. Wen et al IEEE Transactions on Electron Devices, **67** (2020)



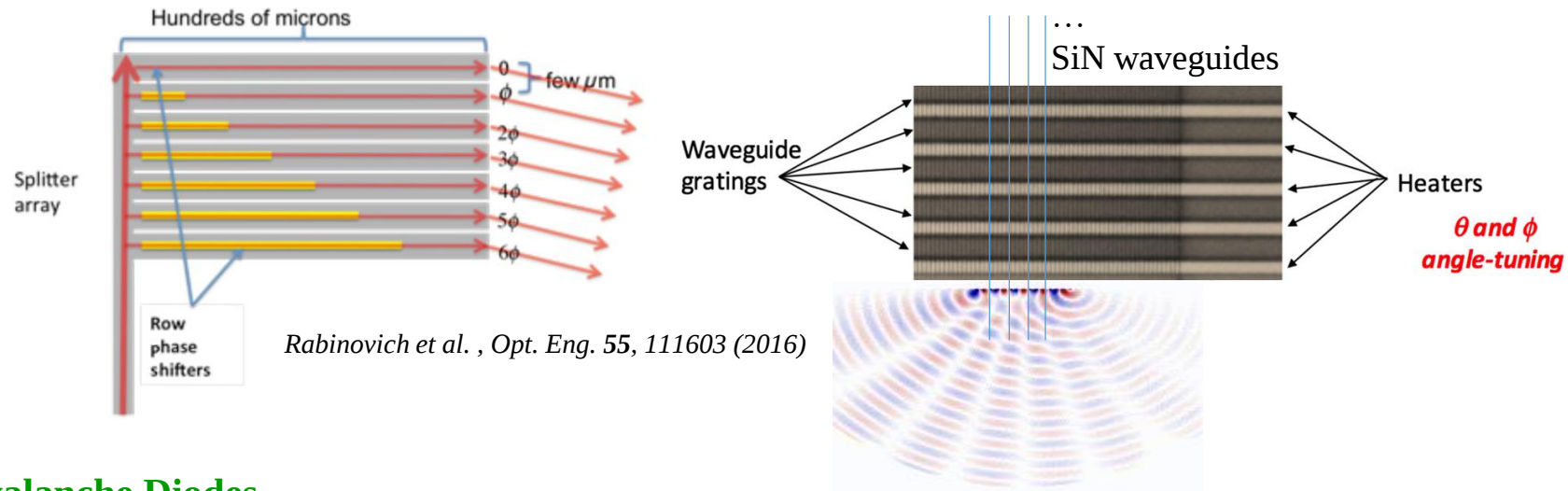
Typical thicknesses of melec layers have a thermal resistance equivalent to TBR. TBR can be a major contribution to the total thermal resistance.



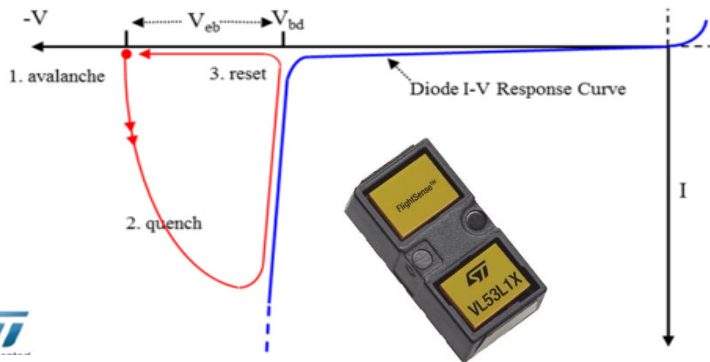
IBM Research / Memory Technologies

## Applications • LIDAR: Beam steering with thermo-optical waveguides

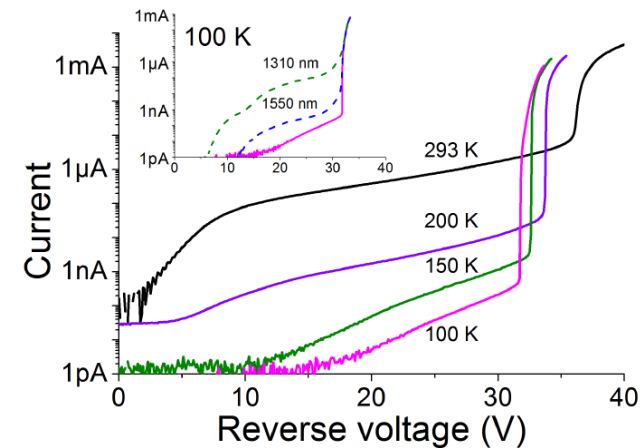
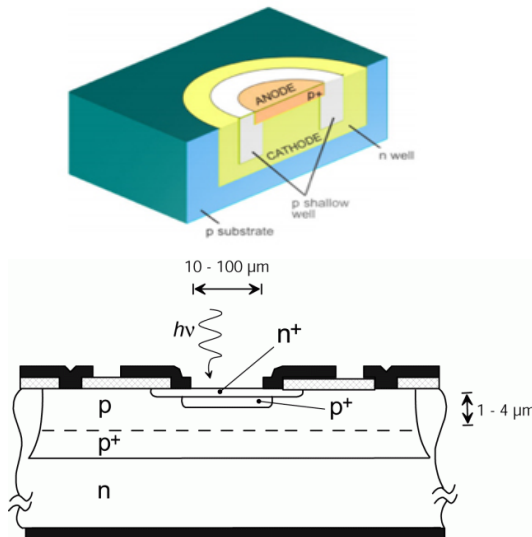
- For IR (905 nm)
- SiN waveguides
- Thermo-optical modulation
- Challenge=go to high frequencies (10-50kHz)
- Need for thermal optimization



## • Detection and imaging : Single Photon Avalanche Diodes



Si 905 nm  
Ge 1300 nm



- Dark Count Rate
- Noise Eq. Power

Can be highly improved through local cooling

R. E. Warbuton et al., Trans. on Electron devices, 60, 3807 (2013)



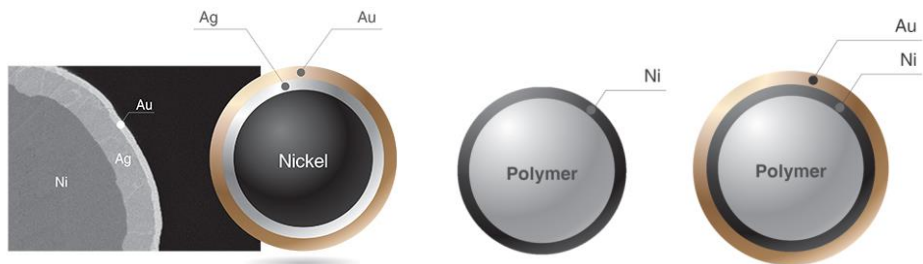
## Techniques • Passive: Thermal interface materials

### TIMs for 5G/AI/Semiconductors

Electrically conductive adhesives - alternative to solders (electronic packaging)

Elastomer socket powder – semiconductor testing

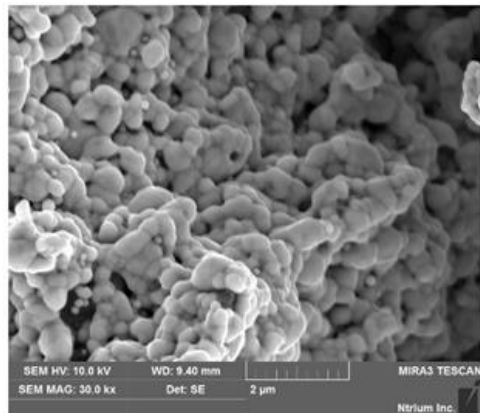
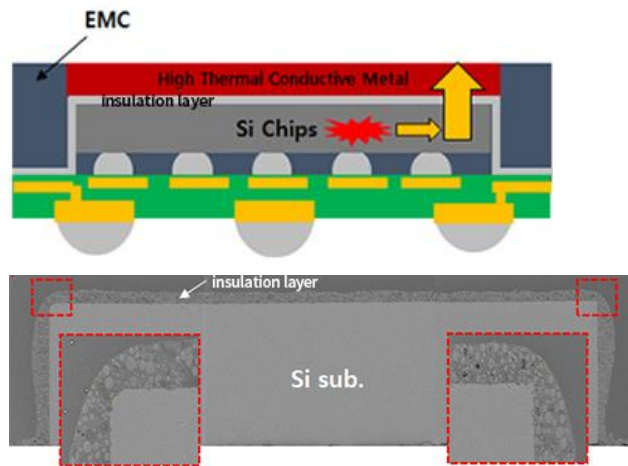
Conductive powder - touch screen panels



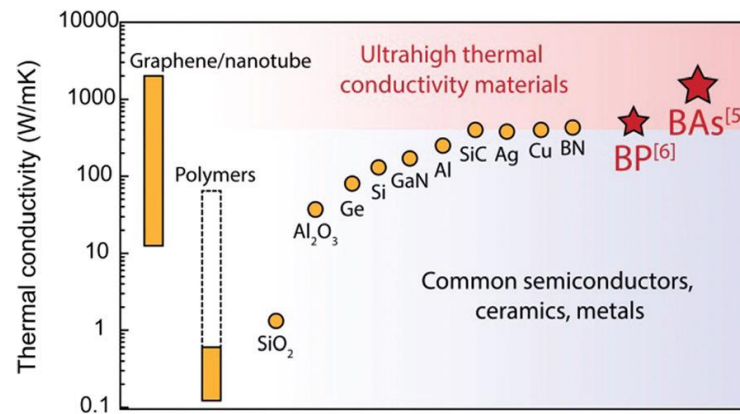
>> Ni + Ag + Au

High thermal ceramic paste for spray – electrical insulator / spray

High Thermal Ag Sintering Paste – high thermal conductivity



### Ultrahigh phonon conductivity materials

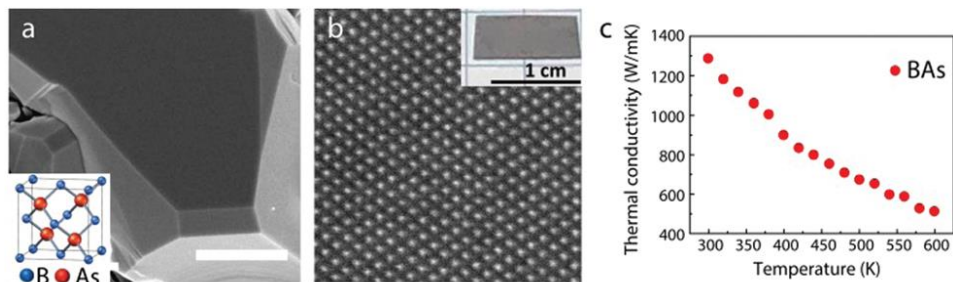


Primarily Synthetic diamond, BN, SiC, Ag, Al, and Cu

**Coefficient of thermal expansion  
should match the heat source**

acoustic phonon bunching  
large acoustic-optical gaps

e.g., BP, BAs





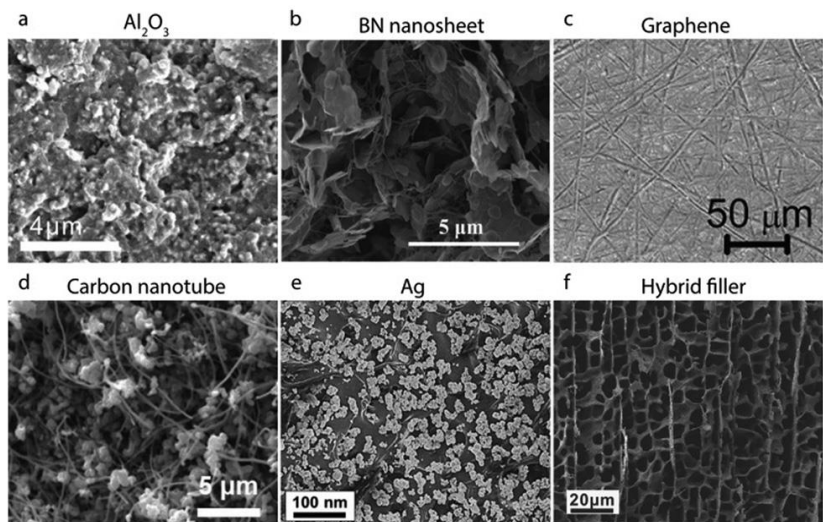
## Techniques

### Passive: Thermal interface materials

## 2D Materials for thermal management

### Fillers for Polymer-Based TIMs

- Ultrahigh thermal conductivity of graphene (semi-metal)
- high conductivity of h-BN (insulator)

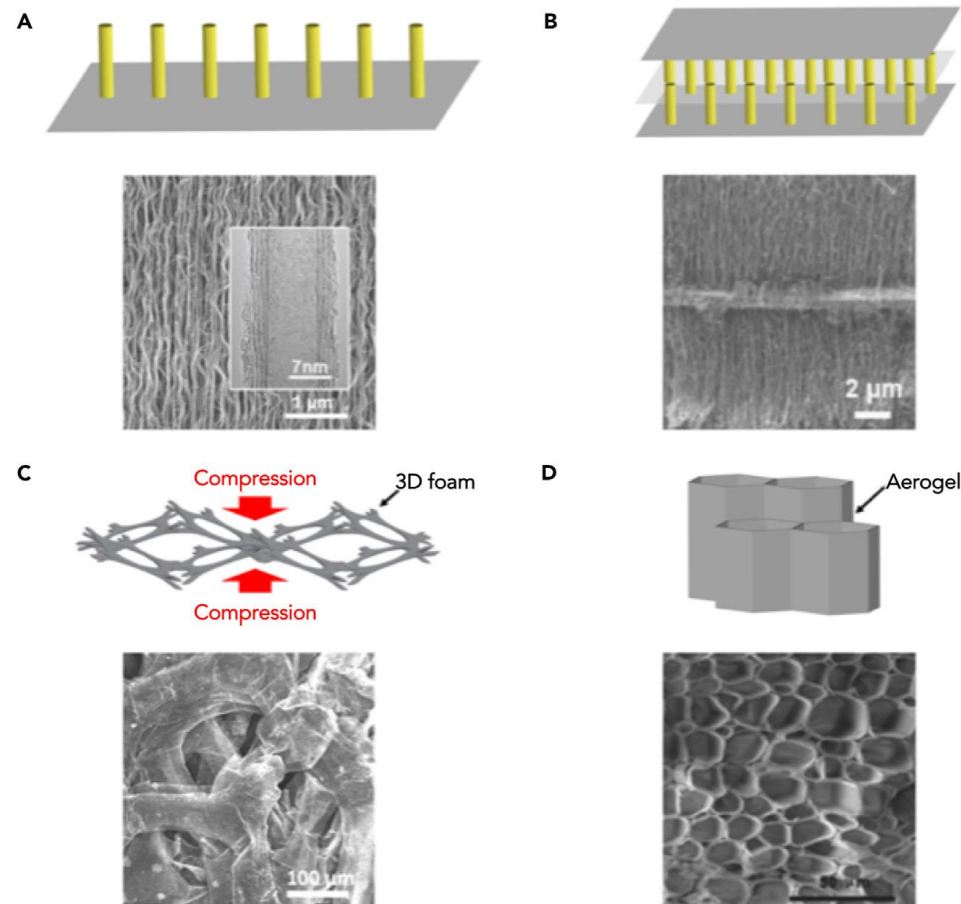


high  $\kappa$  with minimized filler loading

- graphene flakes with Ag particles
- h-BN flakes with SiC nanowires
- Ag flakes with CNTs

### Direct Use for Thermal Management

#### 2D Materials and 3D assemblies



- 3D-Interconnected Graphene and H-BN Macroforms
- Graphene and h-BN Thin Films for Heat Spreaders
- Graphene Fibers for Thermal Management

## ● Challenges and perspectives

### ● Challenges

- Heterogeneity : increased functional density leads to more materials and complex structures
- Mechanical flexibility : can lead to extra thermal resistance due to transfer bonding
- Metrology : TBR in realistic devices stacks
- Modeling : Taking into account non-Fourier conduction in complex structures
- Introduction of nanostructures in devices (NW, membranes) : Leads to new challenges in thermal design
- Paradoxically, high thermal conductivity nanostructures (carbon NW, graphene) can lead to degraded thermal management

### ● Perspectives

- Very high phonon conductivity materials
- Integrated Peltier cooling
- « Heat as a resource » devices (PCRam, PC Switches)



## ● Thermal Management

About this workshop:

- Very rich contents within the GDR and beyond
- We realized that some topics are not covered at all -> Please join !
- This is quite transversal topic and related to other Workshops.

Difficulties:

- Terminology and scope definition

The full presentation,  
including Radiative Cooling and Thermotronics,  
will be presented in next session, October.

Thanks to all contributors :

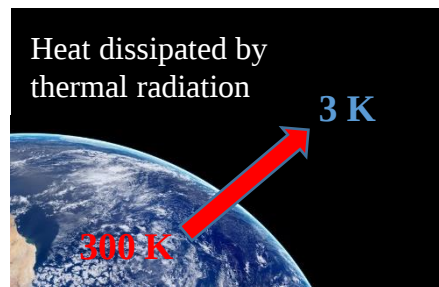
Younès Ezzahri  
Jean-François Robillard  
Philippe Ben-Abdallah  
Jérémy Drévillon  
Nicolas Horny  
Karl Joulain  
Jérémy Maire  
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Stéphane Pailhès  
Roberto Simola



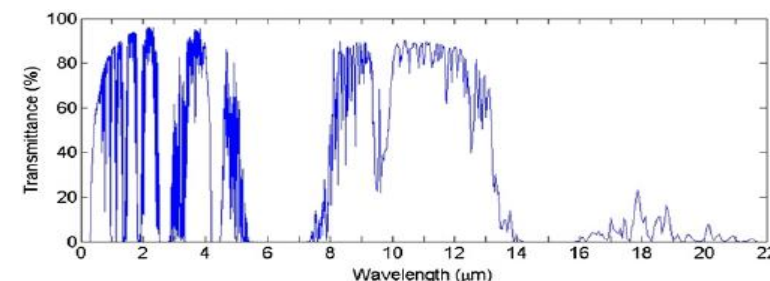
## Principles



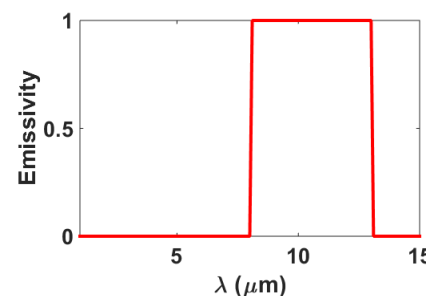
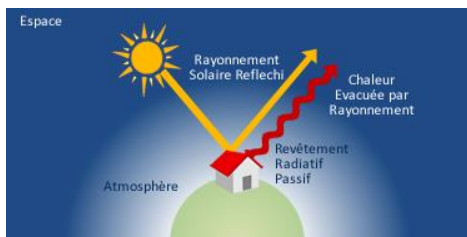
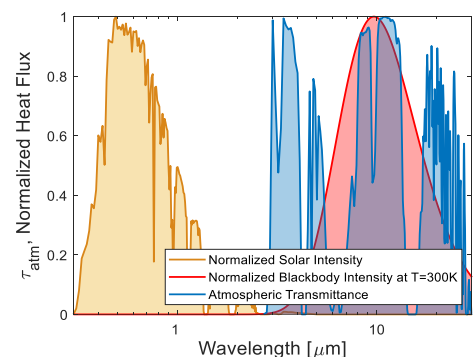
### Natural nocturnal radiative cooling



### Atmospheric transmittance



## Passive daytime radiative cooling



- High emission in the [8, 13]μm interval: *Atmosphere transparency window*
- High reflection in the rest of the spectrum in order to avoid absorption of the solar radiation.

Requires spectral control of the surface emission/reflection.

## Radiative cooling power

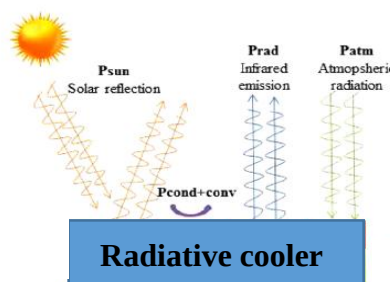
Absorbed incoming power from the sun

Power emitted by the structure

$$P_{cool}(T) = P_{rad}(T) - P_{atm}(T_{amb}) - P_{sun} - P_{cond+conv}$$

Power absorbed due to incident atmospheric radiation

Exchanged power due to conduction and convection



$$P_{rad}(T) = A \int d\Omega \cos \theta \int_0^\infty d\lambda I_{BB}(T, \lambda) \epsilon(\lambda, \theta)$$

$$P_{atm}(T_{amb}) = A \int d\Omega \cos \theta \int_0^\infty d\lambda I_{BB}(T_{amb}, \lambda) \epsilon(\lambda, \theta) \epsilon_{atm}(\lambda, \theta)$$

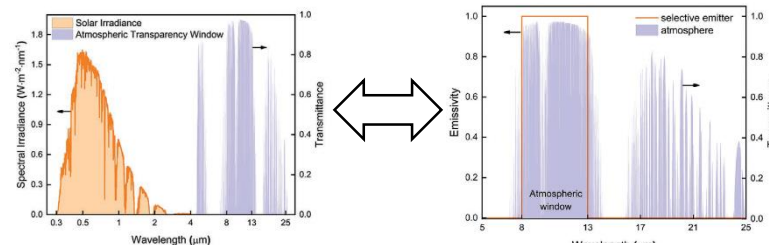
$$P_{sun} = A \int_0^\infty d\lambda \epsilon(\lambda, 0) I_{AM\,sw\,1.5}(\lambda) + A \int d\Omega \cos \theta \int_0^\infty d\lambda I_{solar-diffuse}(\lambda) \epsilon(\lambda, \theta)$$

$$P_{cond+conv}(T, T_{amb}) = Ah_c(T_{amb} - T)$$



## Different approaches

- Nanophotonic approach
- Scalable approach : paint / polymer films



- How to optimize the emission in the transparency spectrum of the atmosphere?
- How to minimize solar absorption?



## Nanophotonic approach: thin films stack

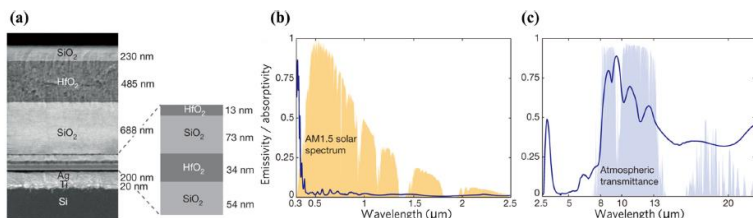
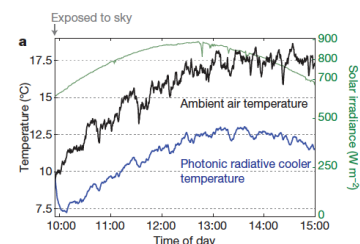
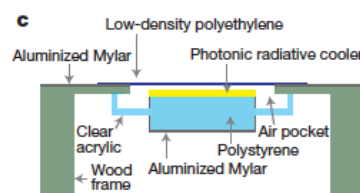


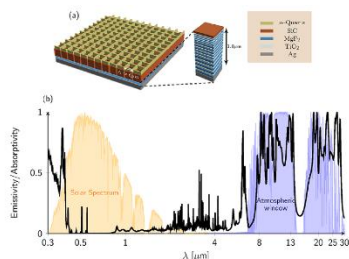
Fig. 13. Scanning electron microscope and spectral characterizations of a photonic radiator (multilayer film) reported in Ref. [13].

AP. Raman et al., Nature, 515, 540 (2014).



R. Family and M. P. Mengüç, Proc Environ Sci, 38, 752 (2017).

## Metamaterials with patterned surface



E. Rephaeli et al., Nano Lett, 13, 1457 (2013).

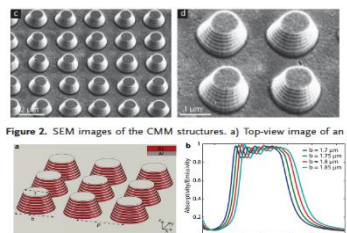


Figure 1. (a) Design of the thermal emitter with multilayer CMM pillar arrays. (b) Calculated emissivity spectra for different bottom diameters of the CMM pillars.

M. M. Hossain et al., Adv. Opt. Mater, (2015).

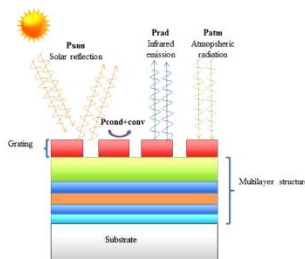
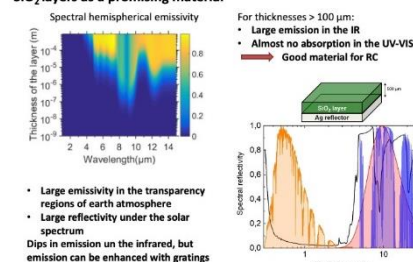


Fig. 1. Schematic of a radiative cooler composed of a multi-layer structure and a grating overhead with the radiative and nonradiative processes taking place.

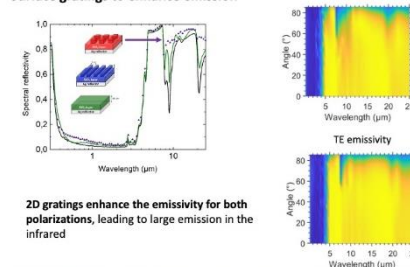
### SiO<sub>2</sub> layers as a promising material



For thicknesses > 100 μm:

- Large emission in the IR
- Almost no absorption in the UV-VIS
- Good material for RC

### Surface gratings to enhance emission



2D gratings enhance the emissivity for both polarizations, leading to large emission in the infrared

A. Hervé, et al., JQSRT, 221, 155 (2018).

## Random polar particle distribution within a polymer

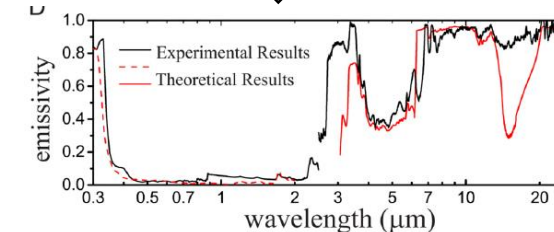
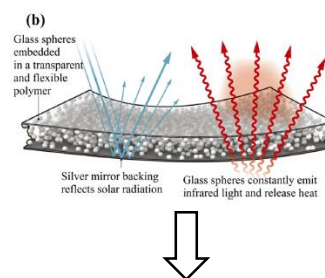


Figure 1. (a) Design of the thermal emitter with multilayer CMM pillar arrays. (b) Calculated emissivity spectra for different bottom diameters of the CMM pillars.

Y. Zhai et al., Science, 355, 1062 (2017).

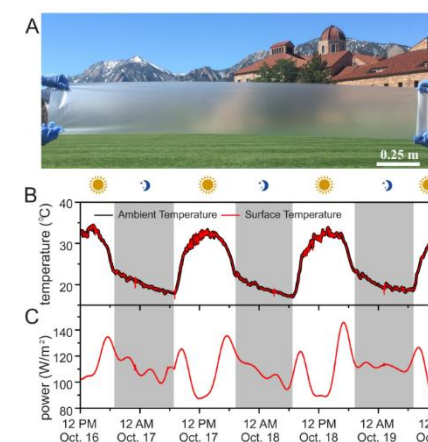
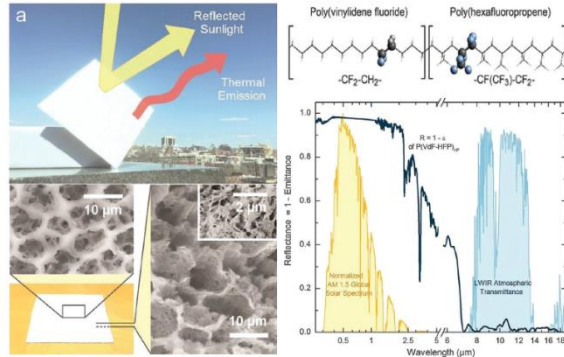


Figure 1. (a) Design of the thermal emitter with multilayer CMM pillar arrays. (b) Calculated emissivity spectra for different bottom diameters of the CMM pillars.



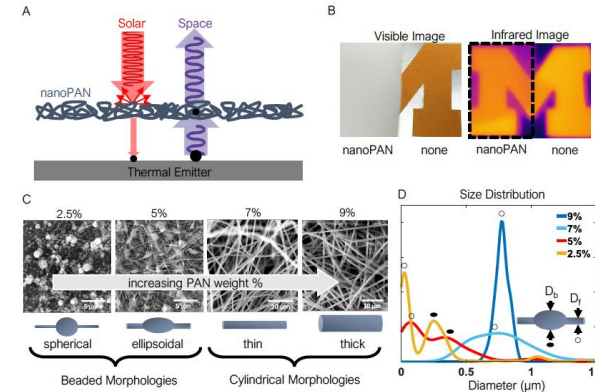
## Different approaches

### Nano/micro porous polymer



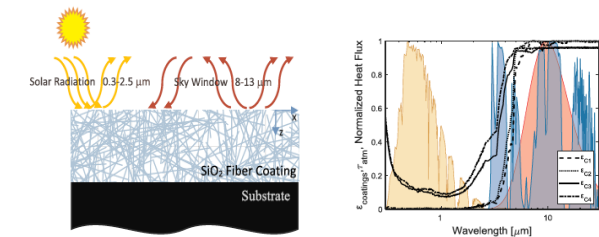
J. Mandal et al., Science 362, 6412 (2018).

### Polymer nanofibers

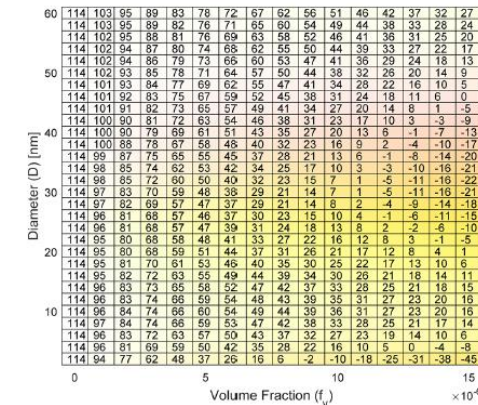
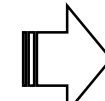
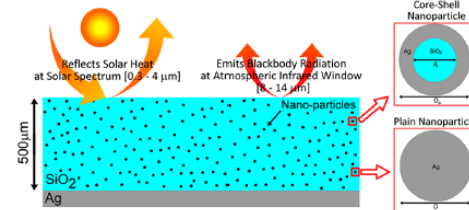


H. Kim et al., ACS Applied Materials & Interfaces, 12, 43553 (2020).

### SiO<sub>2</sub> nanofibers



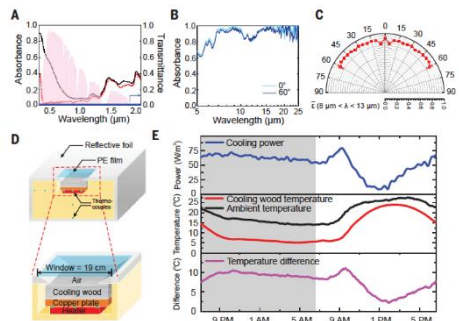
### Colored PDRC



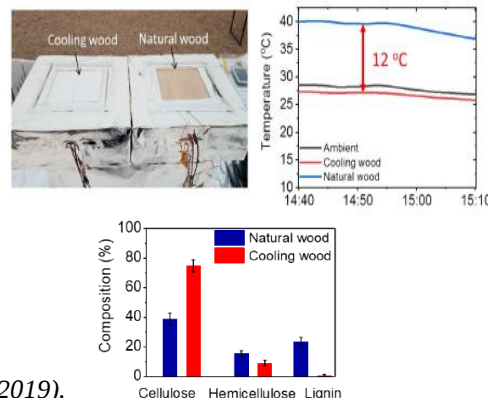
R. Yalçın et al., Solar Energy Materials and Solar Cells, 206, 110320 (2020).

R. Yalçın et al., ACS Photonics, 7, 1312 (2020).

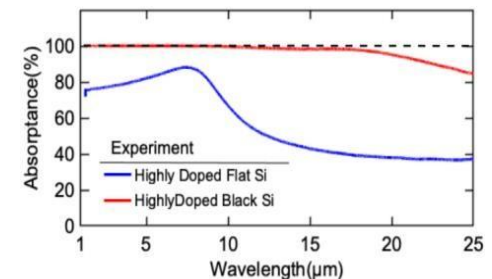
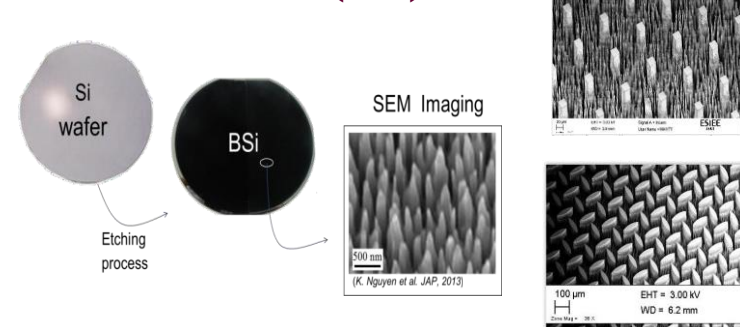
### Delignified wood



T. Li et al., Science, 364, 6442 (2019).



### Black silicon (Bsi)

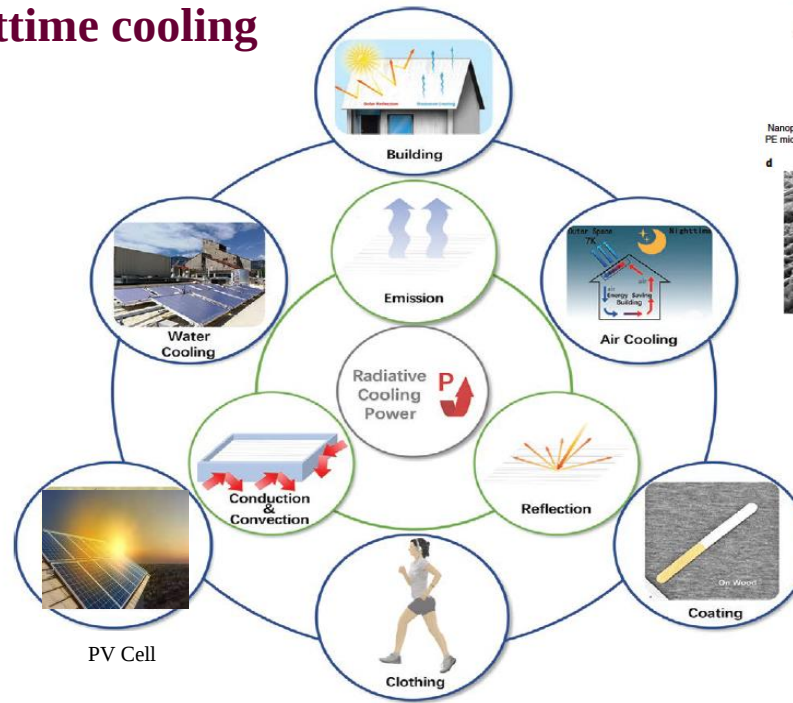


Y. Chen et al., Science Advances, 6, 1 (2020).

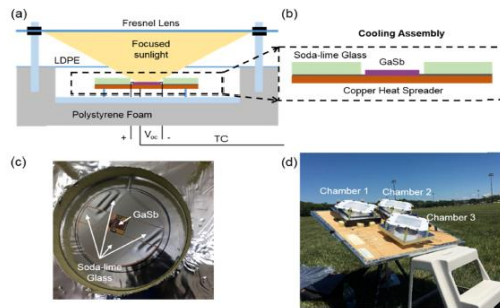


## Applications

### Multiple potential applications: daytime and nighttime cooling



### PV/TPV cooling

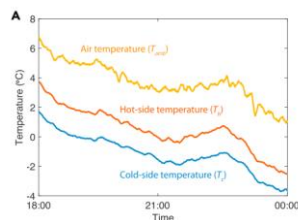
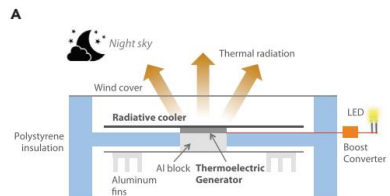


Z. ZHOU et al., Optics Express, 27, A404 (2019).

### Enhancing thermoelectric generation

A. P. Raman et al., Joule, 3, 1 (2019).

Generating light from darkness!



### Start-UP

#### Sky-cool

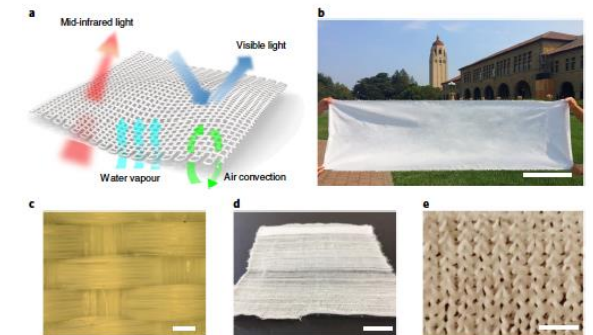
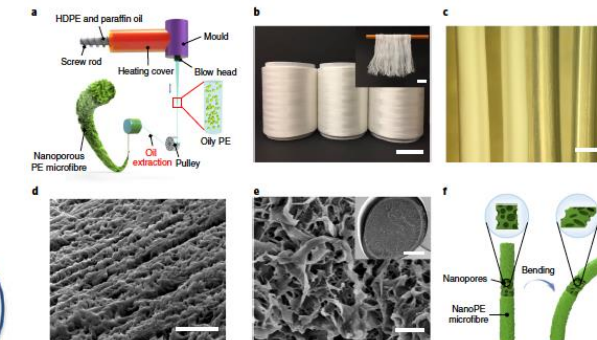


**Aaswath Raman**  
Co-founder, Chief Science Officer  
Aaswath is a professor of Materials Science and Engineering at UCLA. He received his Ph.D. in Applied Physics from Stanford University and is passionate about improving the efficiency of energy systems.



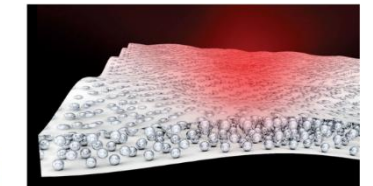
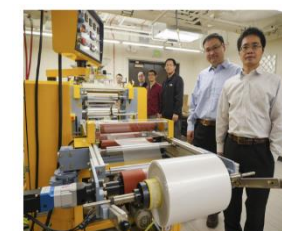
### Human body cooling

Y. Peng et al, Nature Sustainability, 1, 105 (2018).



### Radi-cool

CEO: Ronggui Yang





## ● Challenges and perspectives

### ● Challenges

- Nanofabrication ➡ ➤ Transition to the industrial scale.
- Nano/micro porous structure and nanofibers ➡ ➤ Size control during elaboration (e.g electrospinning of different materials,...)
- Outdoor use: UV radiation / humidity / dust,...
- More precise models for the transparency of the atmosphere and the radiative flux from the environment.

### ● Perspectives

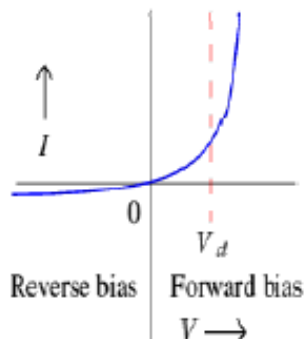
- Numerous proofs of concept: optimization and upscaling.
  - More generally: Optimization of the use of the cold darkness space!



## Historical breakthroughs in electronics

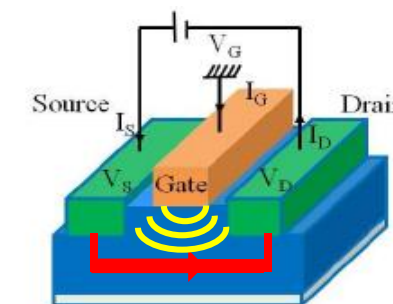
### Diode

F. Braun  
1874



J. Bardeen, W. Brattain,  
W. Shockley  
1947-1951

### Transistor (FET)



- Electrical switching
- Modulation
- Current amplification

## A variety of thermal analogues to the electronic components

N. A. Roberts and D. G. Walker, *IJTS*, 50, 648 (2011).

**"1936: First experimental observation of thermal rectification"**

C. Starr, « The copper oxide rectifier », *Journal of Applied Physics*, 7, 15-19 (1936).

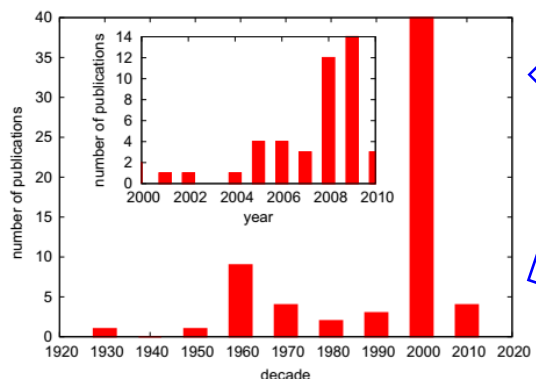


Fig. 1. Number of publications on thermal rectification per decade since 1936.

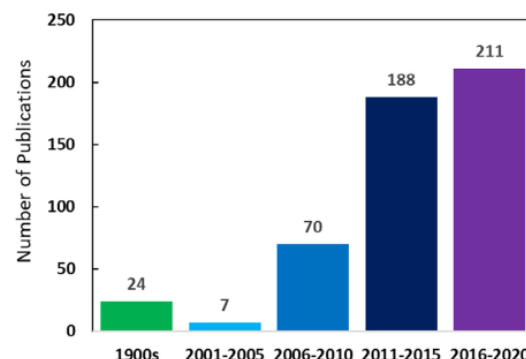
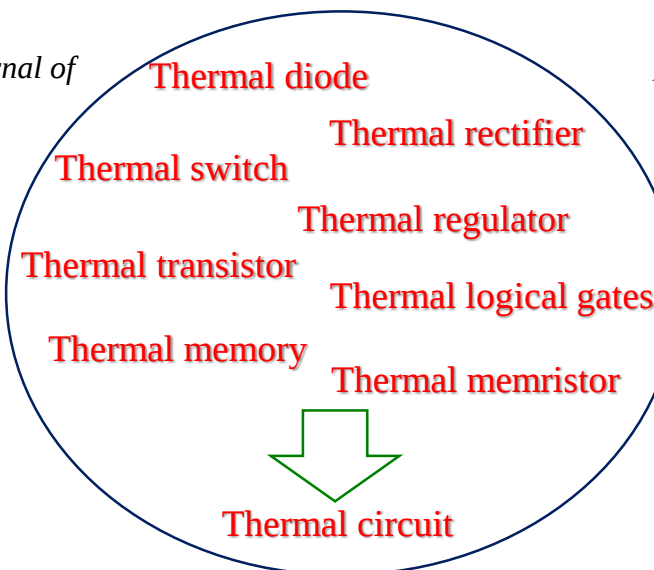


Fig. 2. Number of publications of thermal diode studies from the 1900s to present.



**"No thermal analogue for the electrical inductance!!"**

+

Thermal resistor  
Thermal capacitor

M. Y. Wong, C. Y. Tso, T. C. Ho and H. H. Lee, *IJHMT*,  
164, 120607 (2021).



## Thermal rectifiers and thermal diodes

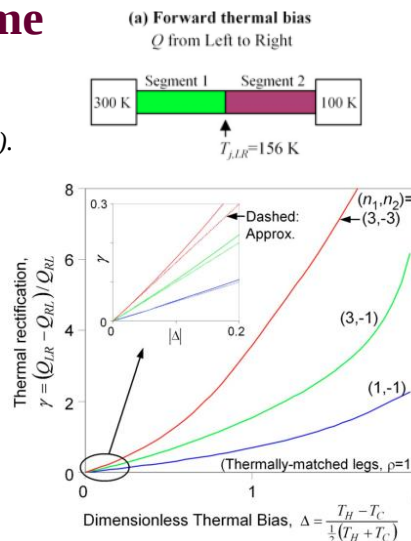
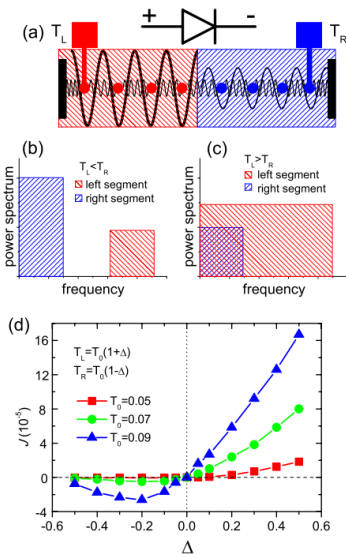
### Different mechanisms

- **Conductive regime:** Asymmetric mismatch in phonon spectra (Nonlinear lattice coupled with harmonic spring) / Asymmetric Kapitza resistance / Asymmetric temperature dependent thermal conductivity / Metal-insulator transition (hysteretic thermal behavior of Phase transition materials PTM) → **Phononics**.
- **Radiative regime:** Resonance modes and broadband (selective emitters, superconductors and PTM) → **Photonics**.
- **Convective regime** also.

### Conductive regime

#### Theory

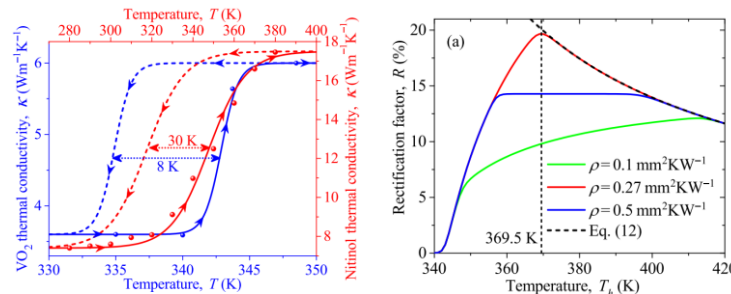
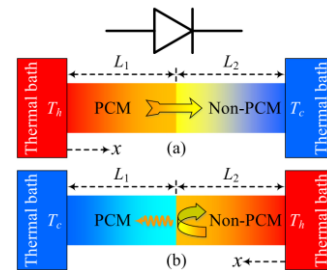
B. Li et al., PRL, 93, 184301 (2004).



C. Dames, JHT, 131, 061301 (2009).

### Rectification factor

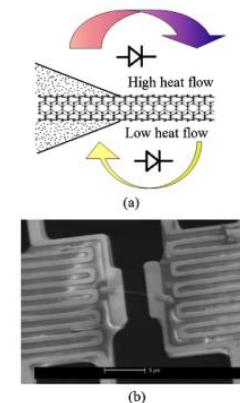
$$R = \frac{|\Phi_F - \Phi_R|}{\max\{\Phi_F, \Phi_R\}}; \frac{|\Phi_F - \Phi_R|}{\Phi_{F,R}}; \frac{|\Phi_F - \Phi_R|}{\Phi_F + \Phi_R}; \frac{\Phi_F}{\Phi_R}$$



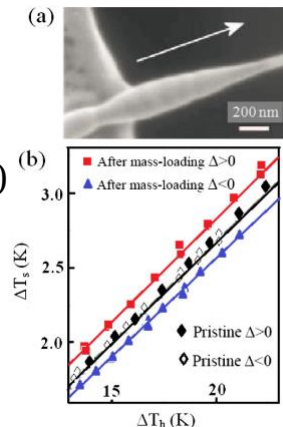
J. Ordonez-Miranda et al., JAP, 123, 085102 (2018).

### Experiment

C. W. Chang et al., Science, 314, 1121 (2006).



Boron nitride (BN) nanotube



### Limitations:

- Kapitza resistance
- Speed of phonons
- Phonon-phonon interactions with strong temperature gradients



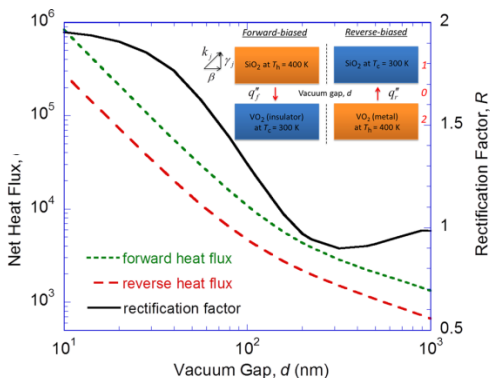
## Thermal rectifiers and thermal diodes

### Radiative regime

#### Theory

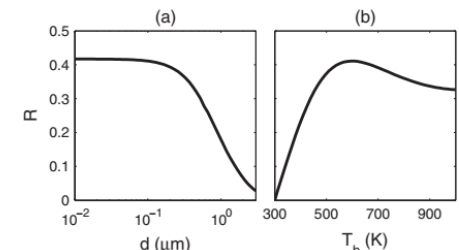
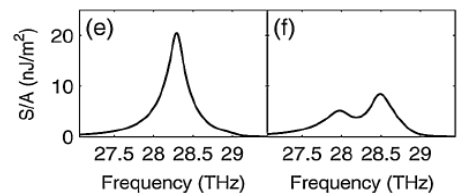
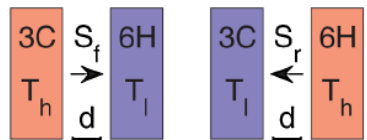
Thin film and bulk  
doped Si

Y. Yang et al., APL, 103, 163101 (2013).

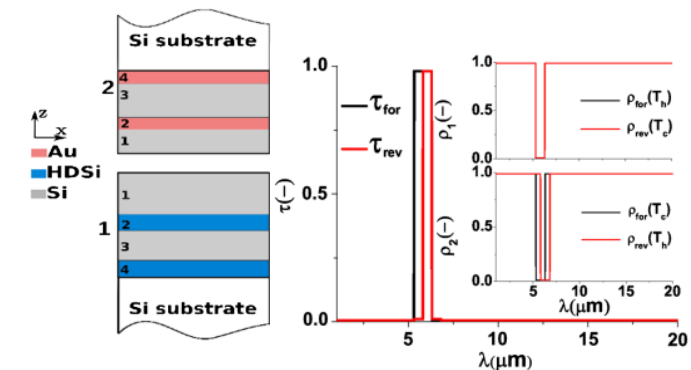


#### Near Field

Two slabs of SiC-3C and SiC-6H

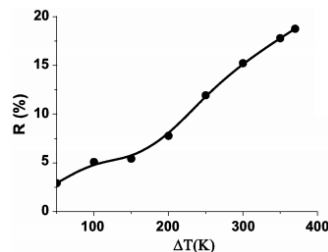


C. R. Otey et al., PRL, 104, 154301 (2010).



E. Nefzaoui et al., AO, 53, 3479 (2014).

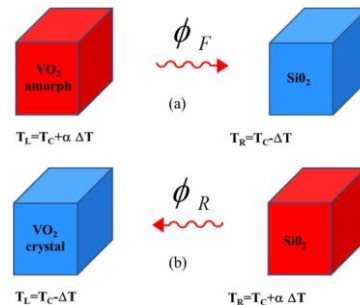
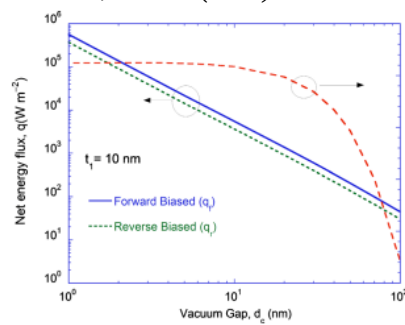
$$R = \frac{|\Phi_F - \Phi_R|}{\text{Max}\{\Phi_F, \Phi_R\}}$$



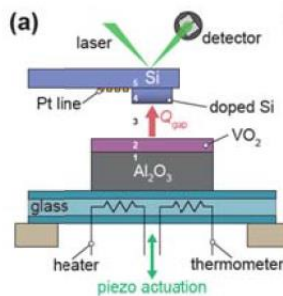
P. Ben-Abdallah and S. A. Biehs, APL, 103, 191907 (2013).

#### Far Field

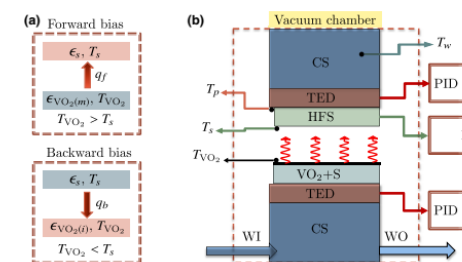
S. Basu and M Francoeur, APL, 98, 113106 (2011).



#### Near Field



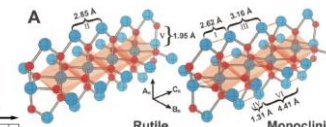
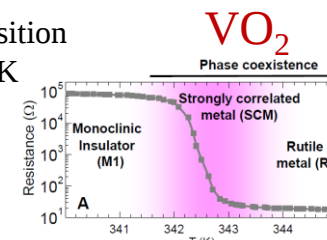
A. Fiorino et al., ACS Nano, 12, 5774 (2018).



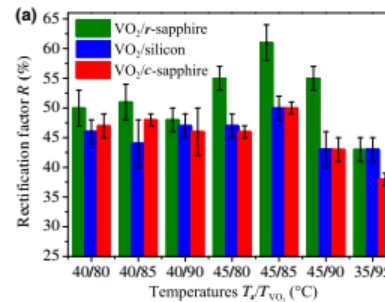
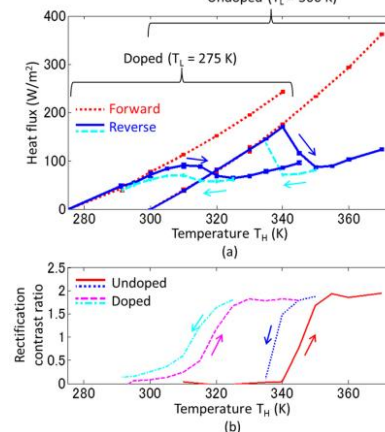
### Experiment

Using phase change (transition) materials  
or superconductors

Mott transition  
at 340 K



K. Ito et al., APL, 105, 253503 (2014).



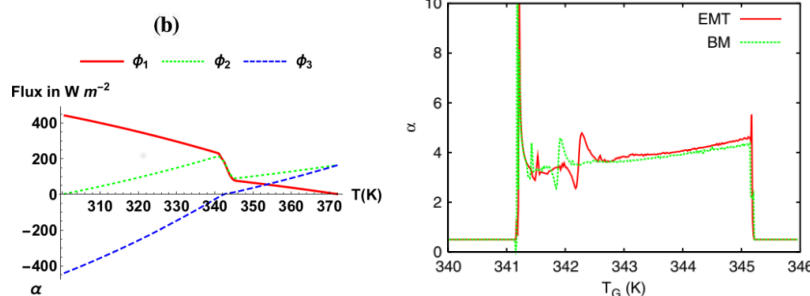
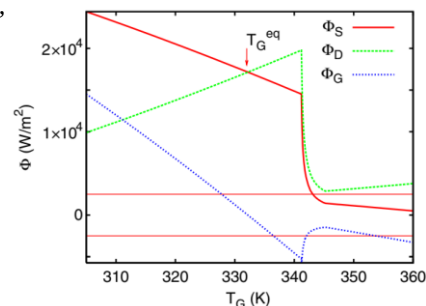
I. Y. Forero-Sandoval et al., PRA, 14, 034023 (2020).



***”Thermal transistor effect ↔ negative differential thermal resistance”***

$$\alpha \equiv \left| \frac{\partial J_D}{\partial J_G} \right| = \left| \frac{R_S}{R_S + R_D} \right| > 1 \text{ SSS } R_S \text{ or } R_D < 0$$

*P. Ben-Abdallah and S. A. Biehs,  
PRL, **112**, 044301 (2014).*


$$\alpha \simeq \frac{\Delta \varepsilon (T_1 - T_c)}{\Delta T (\varepsilon^{met} + \varepsilon^{diel})}$$

*K. Joulain et al., APL, 106, 133505 (2015).*

- 1-Thermal switch
- 2-Flux modulation
- 3-Flux amplification

## SEM images of “AND” and “OR” NanoThermoMechanical gates

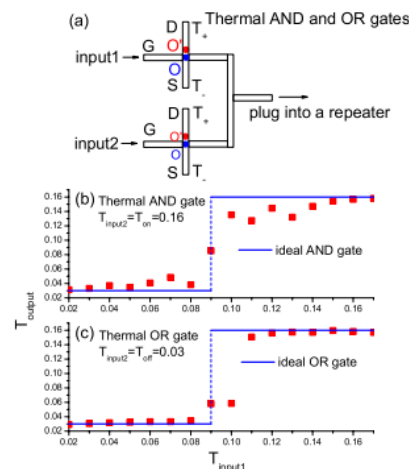


(c) Micrograph of the device structure showing the input and output electrodes. Labels indicate the 'Hot source', 'Output', 'Input 1', and 'Input 2' regions.

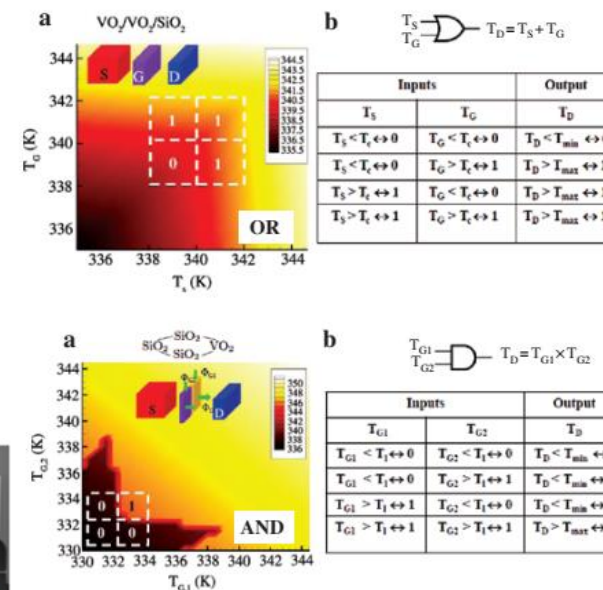
(d) Micrograph of the device structure showing the input and output electrodes. Labels indicate the 'Input 1', 'Input 2', and 'Output' regions.

A. Hamed and S. Ndao, *Scientific Reports*, **10**, 2437 (2020)

L. Wang and B. Li, PRL, **99**, 177208 (2007).



## Radiative regime



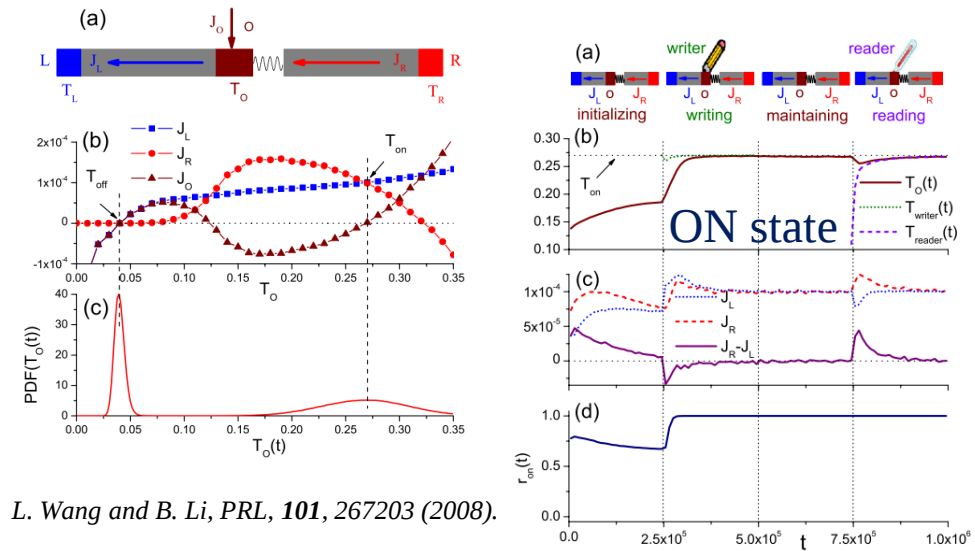
*P. Ben-Abdallah and S. A. Biehs, PRB, 94, 241401(R) (2016).*



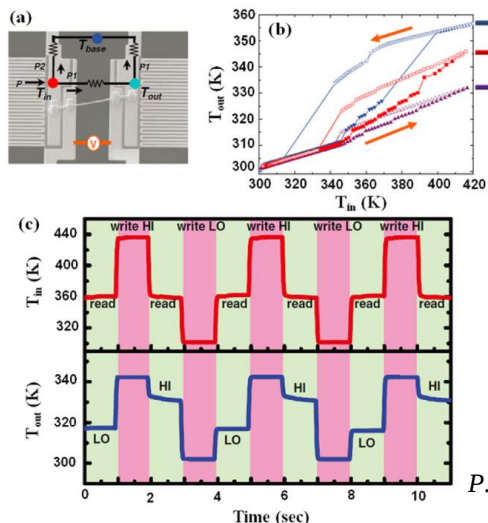
## Thermal logical gates and memories

### Conductive regime

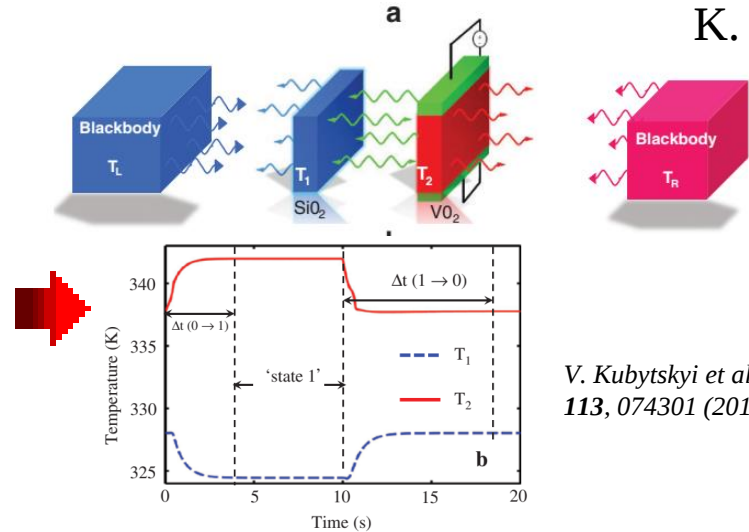
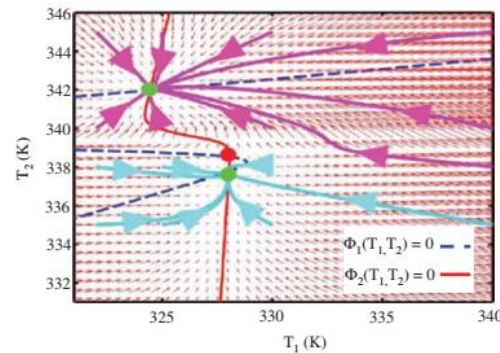
### Theory



### Experiment

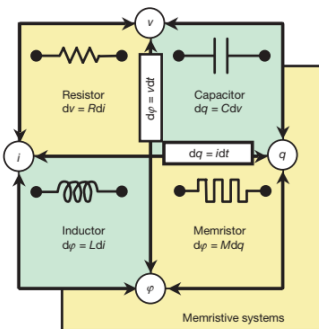


### Radiative regime



## Thermal memristor

Memristor = Memory resistor



Chua's Memristor

$$v = \mathcal{R}(w)i$$

$$\frac{dw}{dt} = i$$

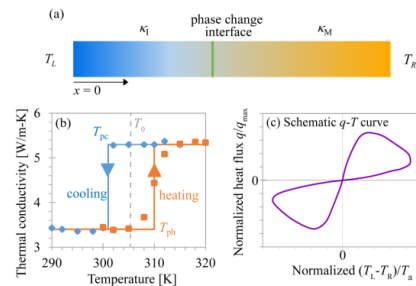
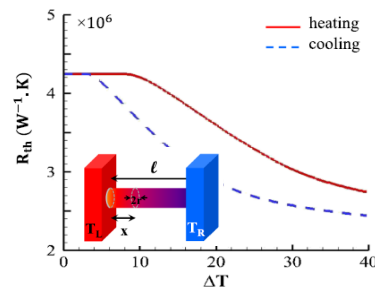
Memristive system

$$v = \mathcal{R}(w,i)i$$

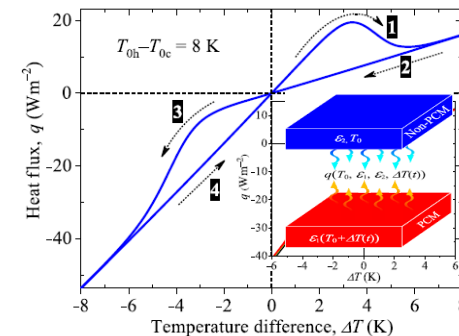
$$\frac{dw}{dt} = f(w,i)$$

- W is a state variable of the device.
- R is a generalized resistance.

### Conductive regime



### Radiative regime

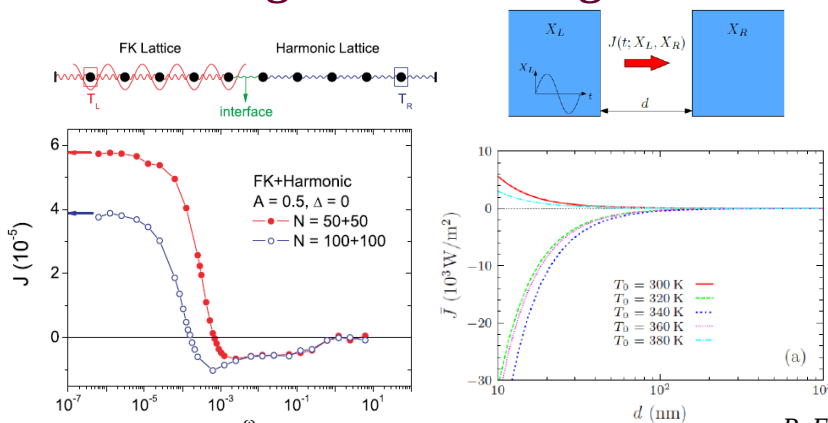


State variable = volume fraction f



## Active control of heat flux

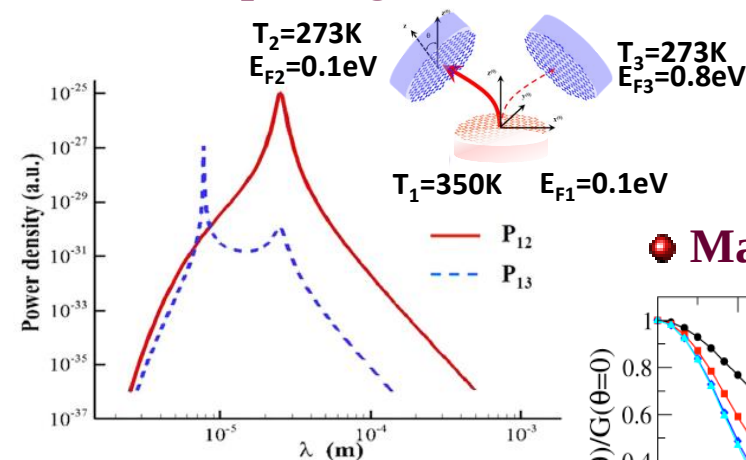
### Shuttling and ratcheting



### Pumping heat against the thermal bias

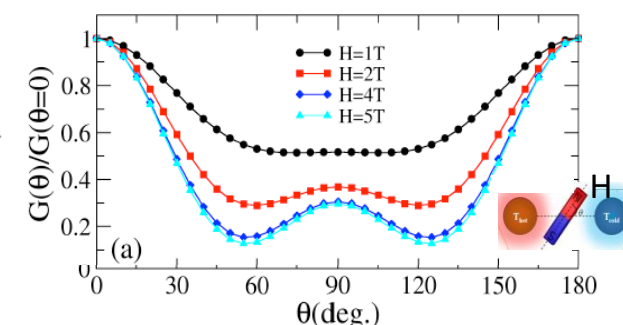
N. Li et al. *Phys. Rev. E* **80**, 011125 (2009); N.-B. Li et al. *Europhys. Lett.* **84**, 40009 (2008);  
I. Latella et al. *Phys. Rev. Lett.* **121**, 023903 (2018).

## Heat splitting

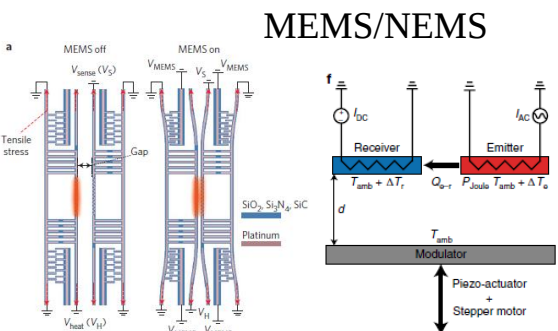


P. Ben-Abdallah et al. *APL*, **107**, 053109 (2015).

## Magnetic control



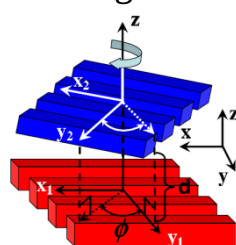
## Mechanical control



R. St. Gelais et al., *Nature Nanon* **11**, 515 (2016).

D. Thompson et al., *Nat. Nano*, **15**, 99 (2020).

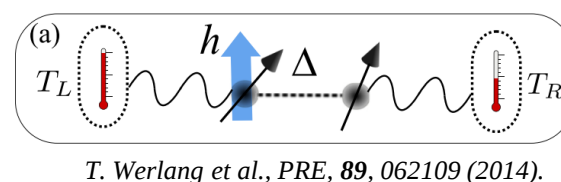
### Gratings rotation



S.-A. Biehs et al. *APL*, **98**, 243102 (2011).

## How about the quantum regime?

### Thermal diode



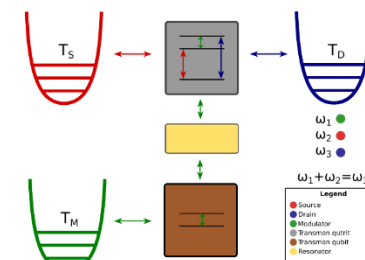
T. Werlang et al., *PRE*, **89**, 062109 (2014).

### Thermal transistor

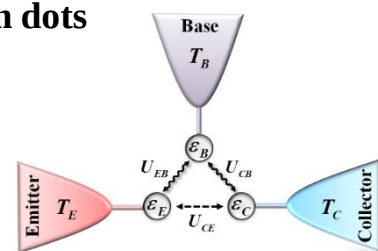
K. Joulain et al., *PRL*, **116**, 200601 (2016).

### Using Superconductors

M. Majland et al., *PRB* **101**, 184510 (2020).



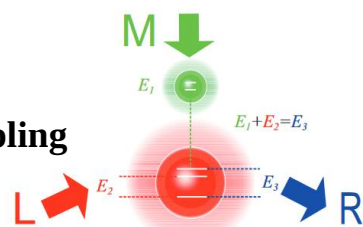
### Using Colomb-coupled quantum dots



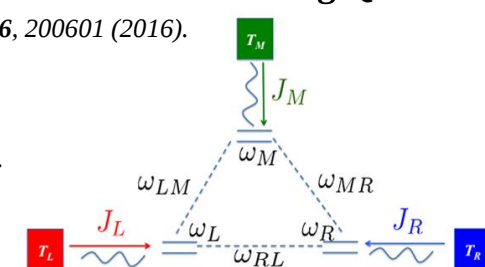
Y. Zhang et al., *EPL*, **122**, 17002 (2018).

### Using Qubit-Qutrit coupling

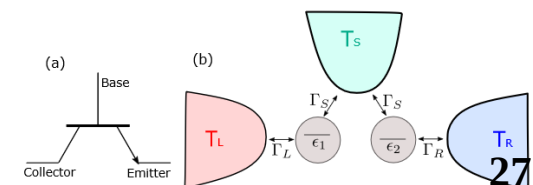
B. Guo et al., *PRE*, **98**, 022118 (2018).



### Using Qubits



G. Tang et al., *Eur. J. Phys. B*, **92**, 27 (2019).





## Challenges and perspectives

### Challenges

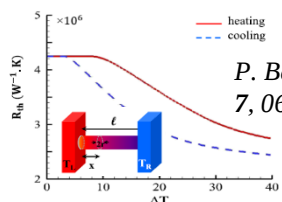
- The operating time scale in nanostructures ( $\sim$ ms to s) is limited by the thermal inertia.



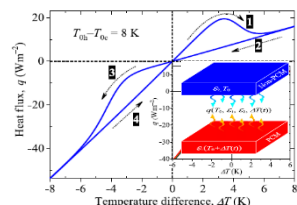
### Perspectives

- Extension of the developed concepts to the conductive regime using Phase Transition Materials (e.g  $\text{VO}_2$ ).
- Exploring and deepening the analysis of the dynamical regime.
- Towards smart hybrid circuits and structures optimizing heat management and electronic operation ...
- Towards a full heat information treatment structure...

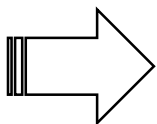
### Memristive behavior



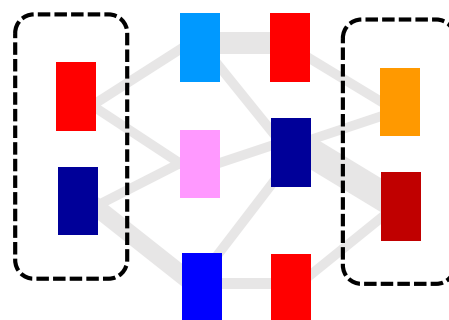
P. Ben-Abdallah, *AIP Advances* 7, 065002 (2017).



J. Ordonez-Miranda et al., *PRL* 123, 025901 (2019).



R. Yu, et al. *Nat Commun* 8, 2 (2017).

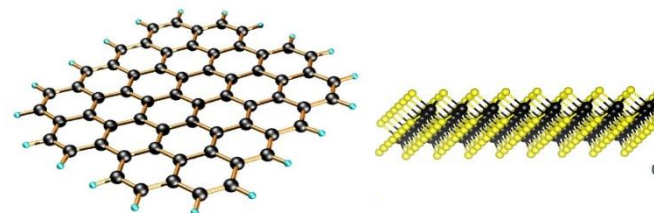


Input

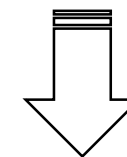
Output

*Neuromorphic computing*

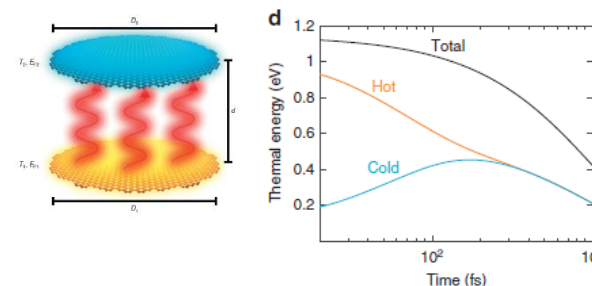
## Two dimensional materials



- Transition metal dichalcogenide monolayers could allow to design thermal transistor operating at submicrosecond scale



## Systems far from equilibrium

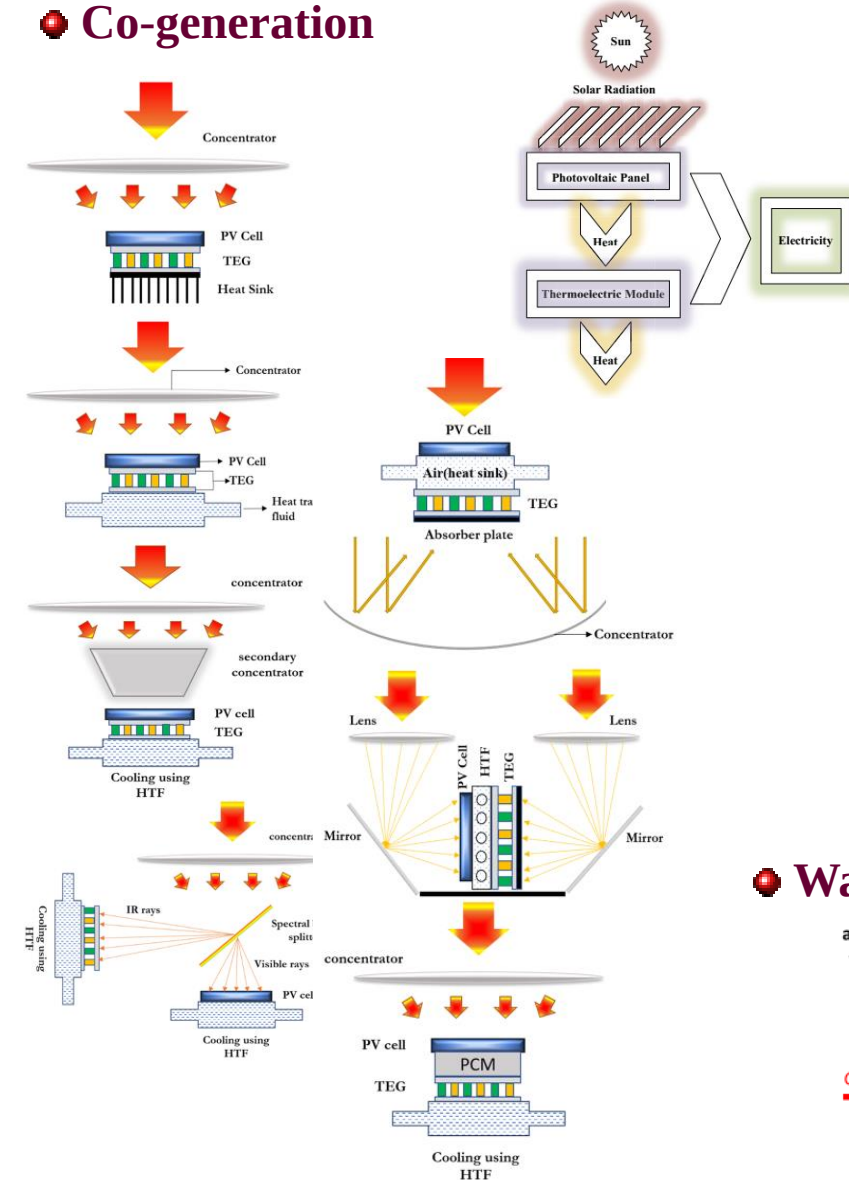


- Electrons and phonons at different temperatures.
- Heat flux control at pico and subpicosecond scale...



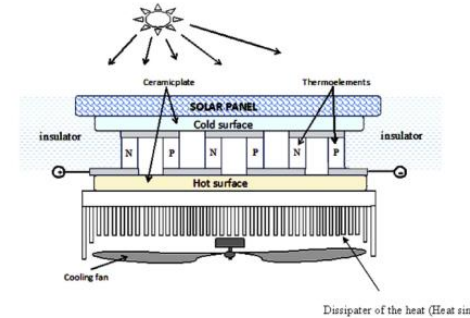
## Hybrid solar PV-TE systems

### Co-generation



S. S. Indira et al., *Solar Energy*, **201**, 122 2020.

### Cooling



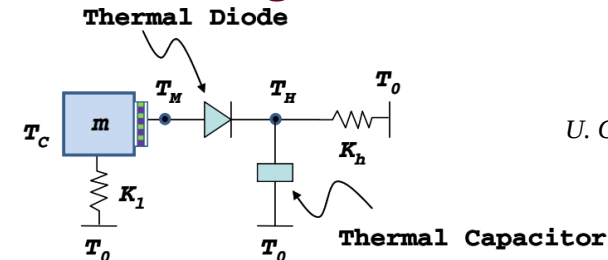
M. Benghanem et al., *Renewable Energy*, **89**, 51 2016.

## Hybrid Thermotronics applications and beyond!

### Solid-state refrigeration using thermal diodes

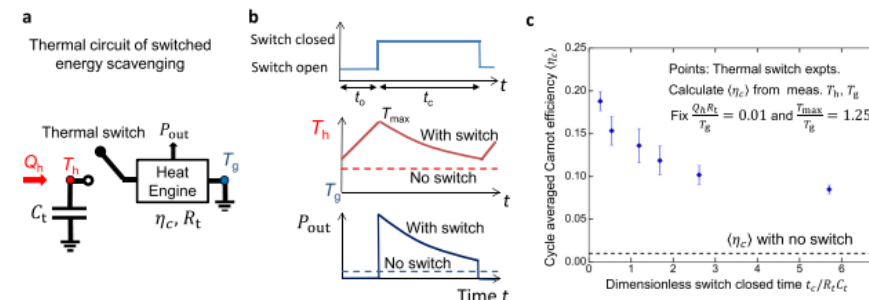
G. Wehmeyer, T. Yabuki, C. Monachon, J. Wu and C. Dames, *Applied Physics Reviews*, **4**, 041304 (2017).

### Enhancing thermoelectric refrigeration



U. Ghoshal and A. Guha, *JEM*, **38**, 1148 2009.

### Waste heat scavenging using switchable and nonlinear thermal devices



G. Wehmeyer, T. Yabuki, C. Monachon, J. Wu and C. Dames, *Applied Physics Reviews*, **4**, 041304 (2017).

